# KENWOOD

# SERVICE WANUAL

TR-7625



2m FM TRANSCEIVER

#### INTRODUCTION/CONTENTS

#### INTRODUCTION

Your KENWOOD Model TR-7625 is an advanced 2-meter transceiver for amateur mobile, and optional fixed station operation.

#### The TR-7625 features:

- ☆ Memory channel (simplex and repeater mode).
- ☆ Memory TX and ±600 kHz repeater TX for repeater operation.
- ☆ 800 channel PLL circuit.
- ☆ Digital frequency display.
- ☆ Dual concentric frequency selector switches.
- ☆ PLL UNLOCK and ON AIR indicators.
- ☆ Subaudible ON/OFF switch (Encoder user installed).
- ☆ Powered tone pad connector with 9V DC on one pin.
- ☆ Pin Mic connector with 9V DC on one pin.
- ☆ TX HI-LOW (Power) switch.
- ☆ Having 25W RF output power.

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of Edition 1040 minimum minimum	

# GENERAL/CIRCUIT DESCRIPTION

#### **GENERAL**

The TR-7625 is a 25W, multi-channel (800 channels) FM transceiver covering 144  $\sim$  147.995 MHz. It features a built-in repeater shift circuit and memory circuit, and provision for connection of an optional (micro-processor) remote control.

#### PLL CIRCUIT

The TR-7625 employs a PLL circuit using SM5111A IC for programmable counter, reference oscillator, frequency divider and phase detector. Frequency division ratio, memory and remote indication functions are all controlled by BCD codes.

#### PLL CIRCUIT BLOCK DIAGRAM

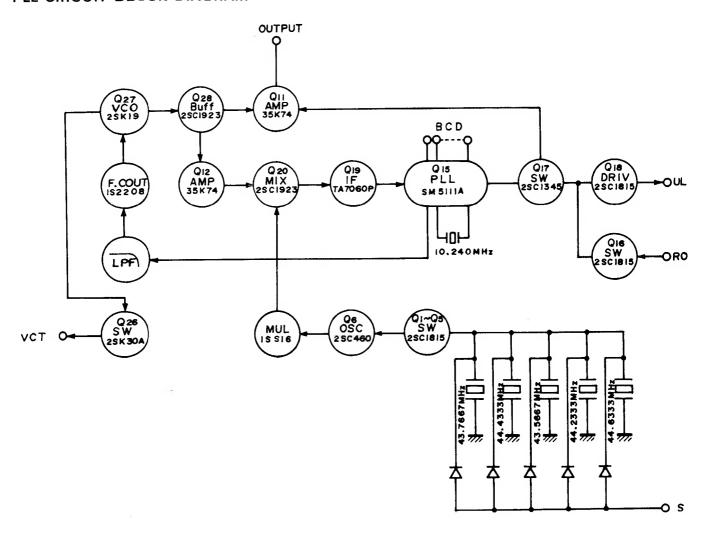


Fig. 1 PLL Circuit

#### CIRCUIT DESCRIPTION

#### 1. Phase Locked Loop

The 130 MHz signal from Q27 passes through the buffer circuit Q28 and is then divided into a synthesizer output by Q11 and a loop output by Q12 respectively. The output from Q12 is mixed with the local oscillator output, tripled by Q6, D21 and Q20 to obtain IF frequency. The IF output is amplified by Q19 and is fed to Q15 where the output is frequency divided as specified by the BCD code and compared with the 10 kHz reference frequency (1/1024 of 10,240 MHz).

The DC output thus obtained passes through the low-pass filter to control the VCO vari-cap diode 1S2208 D26. The output from Q26 controls the transmit frequency bandwidth. When the signal is unlocked, output is shut off by Q17 and indicated by Q18. Q16 shuts off output when the rotary switch is between channel setting positions.

Rx Tx Freq.	Simplex Output	Division	Osc Xtal Freq.	IF Freq.
144.00 MHz	133.3 MHz	200	43.7667 MHz	2 MHz
145.00 MHz	134.3 MHz	300	43.7667 MHz	3 MHz
145.99 MHz	135.29 MHz	399	43.7667 MHz	3.99 MHz
146.00 MHz	135.3 MHz	200	44.4333 MHz	2 MHz
147.00 MHz	136.3 MHz	300	44,4333 MHz	3 MHz
147.99 MHz	137.29 MHz	399	44.4333 MHz	3.99 MHz

Table 1 Division and Frequency

#### 2. +5 kHz Circuit

In the PLL circuit, the reference frequency is controlled in 10 kHz steps. The +5 kHz signal is controlled by varying the local oscillator crystal frequency vari-cap diode, so the frequency division remains unchanged even when the +5 kHz circuit is operated.

The memory circuit also includes the same bit and functions even when the  $\pm 5$  kHz circuit is operating.

#### 3. Shift Circuit

Transmit frequencies can be shifted by changing the local oscillator crystal frequency, as shown below.

144 and 145 MHz bands:

[-] shift 43.5667 MHz [S] 43.7667 MHz

The [+] shift is not available for 144 and 145 MHz bands, [S] occurs at the [+] position.

146 and 147 MHz Bands:

[-] shift 44.2333 MHz [+] shift 44.6333 MHz [S] 44.4333 MHz

#### 4. Memory Shift Circuit

The memory shift (M) is a circuit to shift to the memory frequency during transmission.

#### CONTROL UNIT

Frequency settings are accomplished by the MHz, 100 kHz and 10 kHz rotary switches. The relationship between the frequency and frequency division is shown below.

Frequency	Frequency division
144.000 MHz	200
145.000 MHz	300
145.990 MHz	399
146.000 MHz	200
147.000 MHz	300
147.990 MHz	399

The local oscillator kHz order frequency can be (switch) shifted. Frequency division, set by the rotary switch, is stored in the latch IC's 1, 2 and 3 by pressing the memory input switch. The output from the latch circuit is fed through IC's 4, 5 and 6 in the selector circuit to the PLL circuit by pressing the memory call switch. When this switch is not pressed, the output is fed directly to the PLL circuit. Memory function is effected by latching each switch: The information from each switch is stored by pressing the memory switch.

The stored information remains the same unless the memory switch is pressed once again. Selection of memory output and rotary output is accomplished by the selector circuit. A latched output is obtained by pressing the memory output switch

The signal to the PLL circuit passes through the LED driver circuit and is digitally indicated by LED.

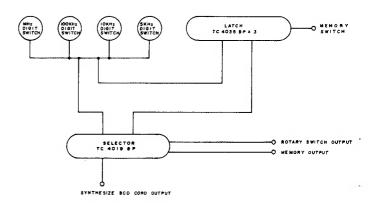


Fig. 2 Block Diagram of Frequency Memory Circuit

#### CIRCUIT DESCRIPTION

#### TRANSMITTER UNIT

The microphone signal passes through the limiter amplifier and FM modulates the 10.7 MHz oscillator. This is mixed with the local oscillator signal to obtain 114  $\sim$  146 MHz signal. The (variable) B.P.F. provides excellent power and spu-

rious characteristics by the use of VCO voltage. The RF power stage uses an M57712H power module manufactured by the Mitsubishi Electric Co., providing high reliability.

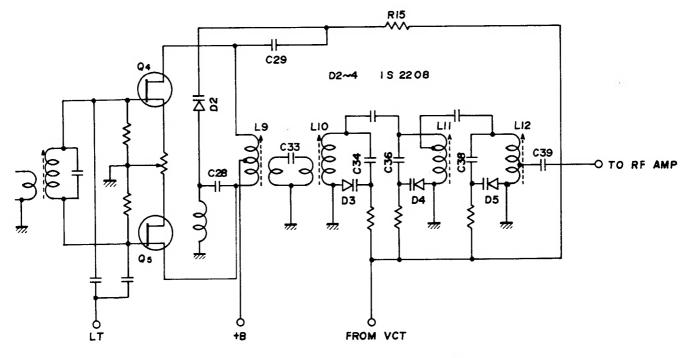


Fig. 3 Variable Transmitter Band Pass Filter Circuit

#### RECEIVER UNIT

The signal from the transmit/receive matching circuit passes through the diode switch and is fed to the 2-stage antenna tuning circuit, 3-stage herical tuning circuit and (MOS FET) RF amplifier. This signal is further fed to the mixer MOS FET where it is converted to a 10.7 MHz signal. The signal thus converted passes through the 2-stage filter and is fed to the 2nd mixer where it is converted to a 455 kHz signal. The 2nd IF signal from the 455 kHz ceramic filter passes through the limiter circuit where it is converted to an AF signal by the ceramic discriminator. This signal is amplified by the audio power amplifier to drive the speaker. The receiver unit includes a noise amplification type squelch circuit. This circuit picks up the noise component in the squelch signal from the discriminator which is amplified and rectified to control the 1st stage AF amplifier.

The characteristic of the discriminator is opposite that of conventional ones to permit connection of a remote control.

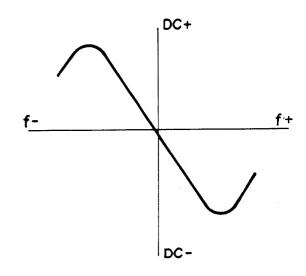


Fig. 4 Discriminator Characteristics

#### SPECIAL SEMICONDUCTOR DATA

#### CAUTION SM5111A

#### **Electrostatic Breakdown Protection**

This item contains built-in input protection circuit to prevent a gate breakdown due to normal ambient static presence to protect the input circuit from damage due to high static or, voltage (in excess of permissible circuit limit), the following points must be observed:

- 1. When the product is not in use, keep all terminals in contact with insulating material (this is done at the factory prior to shipment).
- 2. Soldering iron, testing instruments and other tools should be grounded while in use.
- 3. Do not insert or remove IC from the socket without turning off the power.
- 4. Do not apply signal voltage to the input terminal when power is OFF.
- 5. Do not apply a voltage exceeding the power voltage to the input terminal.

#### **OPERATING SYSTEM**

This product has been developed with C MOS LSI used for PLL circuit. As shown in the block diagram in Fig. 1, it consists of OSC: reference oscillator circuit, DIVIDER: reference frequency dividing circuit, PC: programmable counter, PD: phase comparator, and INV: inverter. A high accuracy feedback type crystal oscillator circuit can be formed by adding a crystal oscillating element, resistor and capacitor between the Qin and Qout terminals of the reference oscillator circuit. This also permits an external signal to be fed to the Qin terminal.

The oscillator output is applied to the reference frequency dividing circuit where it is divided into the desired frequencies of fr1 (1/2048) and fr2 (1/1024) which are the reference signals for the digital phase comparator in the next stage.

The comparison signal (frequency f1) fed to the input terminal FIN of the AMP is amplified and wave shaped, then fed to the input of the programmable counter. The frequency "f1" is frequency converted (fpc) through the program terminals P01 ... P33 (for example, when P01 ... P33 = 1, the programmable counter output is 1/999), and is fed to the phase comparator where it is compared with the reference signal in phase so that a pulse signal, shown below, proportional to the phase difference between the two signal is fed to the output terminal D0.

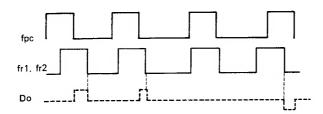


Fig. 5

The table below shows the maximum operation limit and environmental conditions. If any of these values exceeds the given limits, it can be cause of damage to the product or deterioration of quality.

ltem	Symbol	Rating	Unit
Power Supply Voltage	VDD -Vss	-0.3 ∼ +7.5	٧
Input Voltage	Vin	Vss ≦ VIN ≦ VDD	V
Operating Temperature	TA	-30 ~ +70	°C
Storage Temperature	Tstg	-40 ~ + 125	°C
Power Consumption	PD	250	mW
Soldering Temperature		260	°C
Soldering Time		5	sec

Table 2 SM5111A Absolute Maximum Ratings

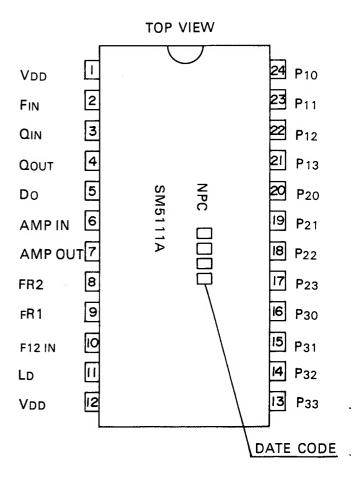


Fig. 6 SM5111A Pin Outline

#### SPECIAL SEMICONDUCTOR DATA

#### 3SK74

#### **SPECIFICATIONS**

Application	VHF RF Amplifier (Mixer)	
Construction	N-Channel • MOS FET (Dual Gate)	
Drain · Source Voltage	Vosx	20V
Gate 1 · Source Voltage	V <sub>G15</sub>	±10V
Gate 2 · Source Voltage	V <sub>G2</sub> s	± 10V
Drain Current	I <sub>D</sub>	25 mA
Allowable Loss	PT	200 mW
Channel Temperature	Тсн	125°C
Storage Temperature	TstG	-5.5 ~ +125°C

Maximum Specifications

# GATE 2 GATE 1 SOURCE

Fig. 7 3SK74 Outline

#### TEST CONDITION

Item	Code	Condition
Drain • Source Voltage	Vosx	V <sub>G1S</sub> = -3V, V <sub>G2S</sub> = 3V, I <sub>D</sub> = 500nA
Drain Current	loss	V <sub>DS</sub> =6V, V <sub>G1S</sub> =0, V <sub>G2S</sub> =3V
Cut-Off Voltage (Gate 1)	VGIS	V <sub>DS</sub> =6V, V <sub>G2S</sub> =0, I <sub>D</sub> =500nA
Cut-Off Voltage (Gate 2)	VG2S	V <sub>DS</sub> =6V, V <sub>G1S</sub> =0, I <sub>D</sub> =500nA
Gate Leak Current (Gate 1)	IGISS	$V_{DS}=0$ , $V_{G1S}=\pm 10V$ , $V_{G2S}=0$
Gate Leak Current (Gate 2)	IG2SS	V <sub>0S</sub> = 0. V <sub>G1S</sub> = 0. V <sub>G2S</sub> = ±10V
Small Signal Transfer Admittance	lyfsi	Vos=6V. Vo2s=3V. 1p=10mA, f=10kHz
Small Signal Input Capacity	Ciss	V <sub>DS</sub> = 6V. V <sub>G2S</sub> = 3V. I <sub>D</sub> = 10mA, f= 1.0 MHz
Small Signal Output Capacity	Coss	Vos=6V, Vozs=3V, Io=10mA, f=1.0 MHz
Small Signal Feedback Capacity	Cass	Vos=6V, Vg2s=3V, Io=10mA, f=1.0 MHz
Output Power Gain	GP	V <sub>DD</sub> = 10V, I <sub>D</sub> = 10mA, f= 200 MHz
Noise Figure	NF	V <sub>DD</sub> = 10V, I <sub>D</sub> = 10mA, f = 200 MHz

#### Maximum Rating of M57712H

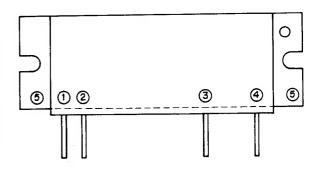
(TA = 25°C, unless otherwise noted)

Item	Symbol	Condition	Value	Unit
Operating Voltage	Vcc		17	V
DC Current	Icc		7	Α
Operating Temperature	TC (OP)		−30 ~ +110	°C
Storage	Тѕтб		$-40 \sim +110$	°C

#### Electrical Characteristic of M57712H

(TA = 25°C unless otherwise noted)

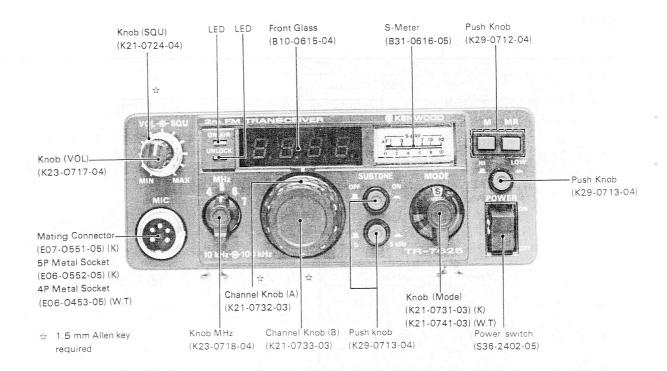
		ol Condition		Value Value			Unit
Item	Symbol			Std.	Max.	Unit	
Output Power	Po	$f = 144 \sim 148 \text{ MHz}, \text{ Vcc} = 12 \text{V}$ Pin = 0.15W, Zg = ZL = 50 $\Omega$	30	34		w	
Total Efficiency	<b>S</b> T	$f=144\sim 148 \text{ MHz}, Vcc=12V$ Pin=0.15W, Zg=ZL=50 $\Omega$	45	50		%	
2nd Harmonic Radiation		$f = 144 \sim 148 \text{ MHz}, Vcc = 12V$ Pin = 0.15W, Zg = ZL = $50\Omega$			-25	dВ	
Greater than 3rd Harmonic Radiation		$f = 144 \sim 148 \text{ MHz}, Vcc = 12V$ Pin = 0.15W, Zg = ZL = $50\Omega$			-30	dВ	
Input VSWR	Pin	$f = 144 \sim 148 \text{ MHz}, \text{ Vcc} = 12V$ Pin = 0.15W, Zg = ZL = $50\Omega$		2.0	2.8		
Output VSWR	Рочт	$f = 144 \sim 148 \text{ MHz}, \text{Vcc} = 12\text{V}$ Pin = 0.15W, Zg = ZL = $50\Omega$		1.5			
Impedance		Note	∞ : 1				

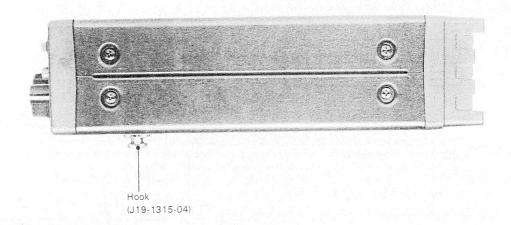


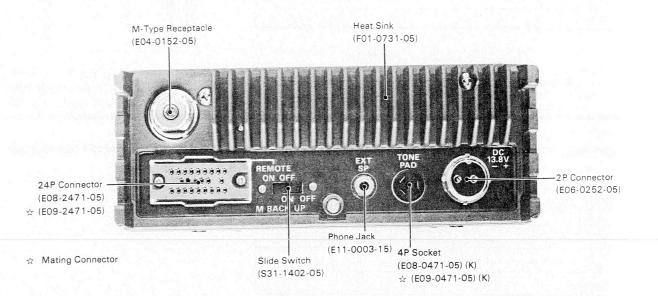
- 1. Input Terminal (RFI)
- 2. Power Supply of Drive Stage (DRB)
- 3. Power Supply of Output Stage (FIB)
- 4. Output Terminal (RFO)
- 5. GND

Fig. 8 M57712H Outline

#### **OUTSIDE VIEWS**

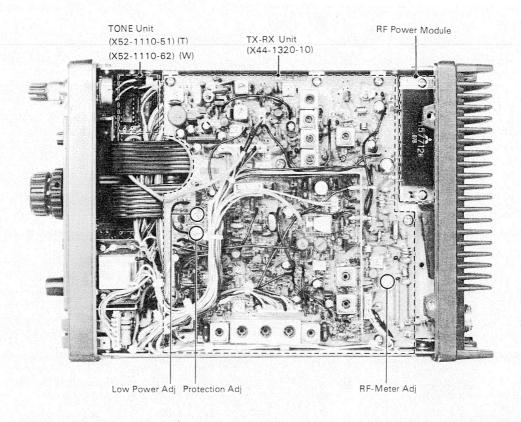




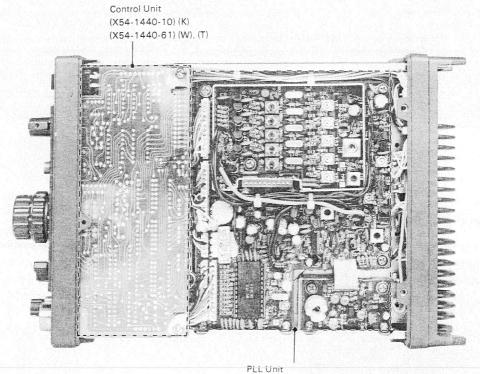


#### INSIDE VIEWS

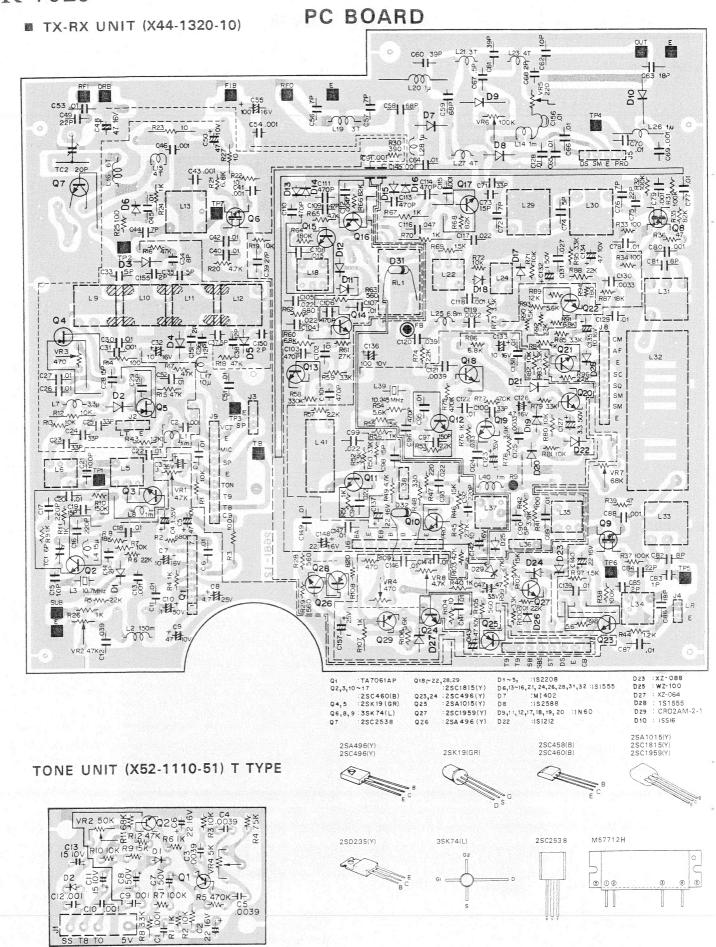
#### TOP VIEW



#### **BOTTOM VIEW**

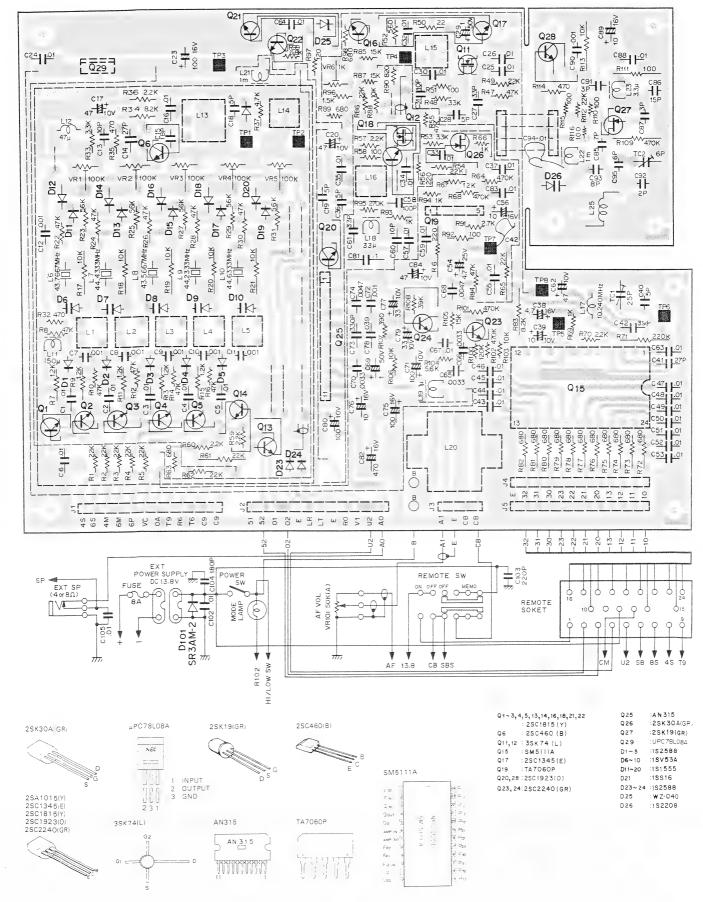


(X50-1580-10) (K) (X50-1580-61) (W), (T)



#### PC BOARD

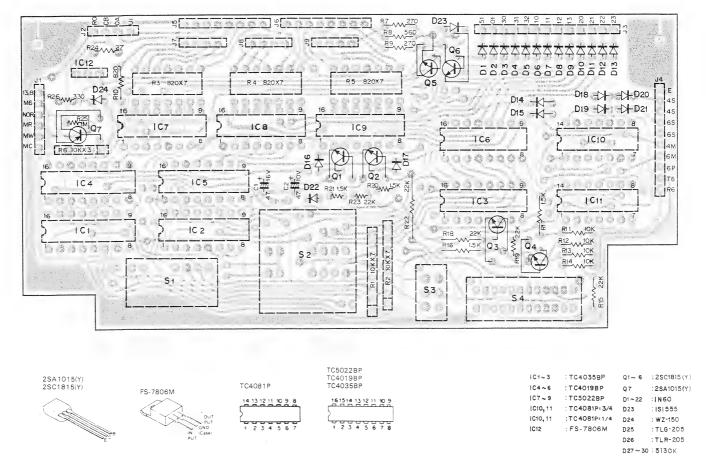
#### ■ PLL UNIT (X50-1580-10)



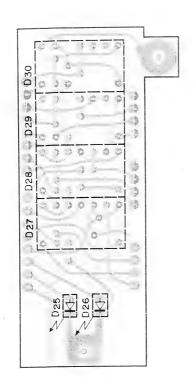
# TR-7625

#### PC BOARD

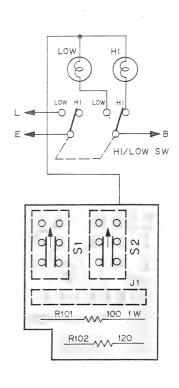
#### **■ CONTROL UNIT (X54-1440-10)**



J25-2668-04 (Indicator)



J25-2664-04 (Switch)

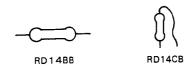


#### NOTE:

Except special types (example' cement, metal film, etc.) resistors are not detailed in the PARTS LIST. Refer to the schematic diagram of the PC board illustration for value. Resistors not otherwise detailed are carbon type (1/4 or 1/8W). Order carbon resistors according to the following example:

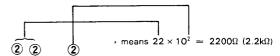
A carbon resistor's part number is RD14BB 2E222J.

1. Type of the carbon resistor



2. Wattage

3. Resistance value



Significant figure Multiplier

Example:

 $\begin{array}{c} \textbf{221} \,\rightarrow\, \textbf{220}\Omega \\ \textbf{222} \,\rightarrow\, \textbf{2.2k}\Omega \end{array}$ 

 $222 \rightarrow 2.2k\Omega$   $223 \rightarrow 22k\Omega$ 

 $\textbf{224} \, \rightarrow \, \textbf{220k}\Omega$ 

225  $\rightarrow$  2.2M $\Omega$ 

**GENERAL** 

☆: New parts

Ref No	Parts No.	Descrip	Re- marks	
		CAPACITORS		
C101	CC45SL2H100D	Ceramic 10pF	±0.5pF	
C102,105	CK45F1H103Z	Ceramic 0 01 µF	+80%-20%	
C103	CK45B1H221K	Ceramic 220pF	±10%	
C104	CC45SL1H181J	Ceramic 180pF	±5%	
	SE	MICONDUCTOR		
Q101	V30-1043 06	Power module M57	712H	ជំ
Q102	V04-0880-16	Transistor 2SD	880 (Y)	
D101	V11-0171-05	Diode SR3/	4M-2	
D102	V11-0076-05	Diode 1S	1555	<u> </u>
		COIL		
L101	L34-0814-05	Coil 4ø4T		位
	PC	TENTIOMETER		
VR101	R19-9403-05	10kΩ (A) 50k (B)		
	M	SCELLANEOUS		
	A01-0734-13	Case (A)		☆
_	A01-0735-03	Case (B)		☆
_	A20-2345-03	Die cast panel (Fron		☆
	A20-2347-03	Die cast panel (Fron		☆
-	A20-2346-03	Die cast panel (Fron	t) (T)	☆
				☆
	B05-0707-04	Speaker grill cloth		☆
_	B10-0615-04	Front glass		☆
-	B31-0616-05	Meter		☆
-	B30-0802-05	Pilot lamp (white)		
-	B30-0803-05	Pilot lamp (Blue)		
_	B30-0106-05	Pilot lamp (Small)	(14)	
	B42-1660-04	Sticker	(K)	
-	B46-0058-00	Warranty card	(K)	
-	B50-2639-00	Operating manual	(K)	☆
-	B50-2641-00	Operating manual	(W)	☆
	B50-2640-00	Operating manual	(T)	☆
-	E04-0152-05	M type receptacle	O) //4/\/T1	1
-	E06-0453-05	4P metal socket (MI		\ \( \times \)
-	E06-0552-05	5P metal socket (Mi	•	☆ ~
-	E07-0451-05	4P metal consent	(W) (T)	☆ ^
_	E07-0551-05	5P metal consent	(K)	☆

Ref No	Parts No	Description	Re- marks
	E06-0252-05	2P connector (Jack)	
	E08-0471-05	4P socket (TONE PAD) (K)	
_	E09-0471-05	4P plug (TONE PAD) (K)	
+	E11-0003-15	Earphone jack	
_	E12-0001-05	Phone plug	
-	E23-0043-04	Antenna ground lug	
-	E23-0015-04	Earth lug	
_	F01-0731-05	Heat sink	ri:
_	F05-8021-05	Fuse (8A)	
_	F20-0078-05	Insulating plate	
	F29-0014-05	Insulating washer	
_	G02-0505-05	"D" spring knob	
	G11-0054-14	Insulating cushion × 2	
_	G13-0616-14	Cushion (A) × 2	公
_	G13-0617-04	Cushion (B)	☆
_	G13-0618-04	Cushion × 2 (angle)	
_	H01-2615-03	Carton (K) (W)	ជ
_	H01-2616-03	Carton (T)	ជ
-	H10-2519-12	Packing fixture	☆
~	H10-2501-03	Styren foam cushion	
	H20-1408-03	Protective cover	☆
_	H25-0049-03	Accessory bag	
_	H25-0079-04	Polyethylene bag (MIC)	
	H25-0103-04	Polyethylene bag (Cord)	
_	J21-2607-03	Mount-base	
_	J21-2608-03	C type angle	☆
-	J51-0006-15	Snap-lock × 2	
_	J61-0019-05	Vinyl tie	
-	K21-0724-04	Knob (Outside) SQU	
-	K21-0731-03	Knob (Mode) (K)	☆
-	K21-0732-03	Channel Knob (A)	ជ
_	K21-0733-03	Channel Knob (B)	公
-	K21-0741-03	Knob Mode (W) (T)	☆
	K23-0717-04	Knob VOL	<b>☆</b>
-	K23-0718-04	Knob MHz	☆
	K29-0712-04	Push knob (square) × 2 M, MR	公

Ref No	Parts No	Description		Re- marks
_	K29-0713-04	Push knob (circle) × 3		☆
_	N09-0008-04	Screw × 4 (angle)		
_	N14-0009-04	Nut × 4 (angle)		
	N15-1040-46	Flat washer × 4 (angle)		
_	N15-1060-46	Flat washer × 4 (angle)		
l –	N16-0060-46	Spring washer × 4 (angle)		
_	N99-0304-04	Allen head bolt × 4		☆
-	S31-1402-05	Slide switch (remote)		
-	S36-2402-05	Power switch		
_	S40-2409-05	Push switch (M)		☆
_	S40-2404-05	Push switch (MR)		
	S40-2403-05	Push switch SUB, HI/LOW		
_	S40-2406-05	Push switch TONE (W)		
_	T07-0201 05	Speaker (8Ω)		
	T91-0310-05	Microphone	(K)	
_	T91-0302-05	Microphone	(W)	☆
-	T91-0301-05	Microphone	(T)	
	W01-0401-04	Allen key (angle)		
-	X44-1320-10	TX-RX unit		☆
-	X50-1580-10	PLL unit	(K)	☆
-	X50-1580-61	PLL unit	(W) (T)	☆
-	X52-1110-62	TONE unit	(W)	☆
-	X52-1110 51	TONE unit	( <b>T</b> )	☆
-	X54-1440-10	CONTROL unit	(K)	☆
-	X54-1440-61	CONTROL unit	(W) (T)	☆
-	X42-1170-01	DC cord Ass'y		☆

# TX-RX Unit (X44-1320-10)

Ref No	Parts No	Description			Re- marks			
	CAPACITOR							
C1	CK45F1H103Z	Ceramic	0 01μF	+80, -20%				
C2	CK45B1H102K	Ceramic	0 001μF	±10%				
C3.4	CS15E1VOR1M	Tantalum	0 1 μF	35WV				
C5	CE04W1A470	Electrolytic	47μF	10WV				
C6	CK45F1H103Z	Ceramic	0 01μF	+ 80, -20%				
C7	CE04W1C100	Electrolytic	10μF	16WV				
C8	CE04W1E4R7	Electrolytic	47μF	25WV				
C9	CE04W1A470	Electrolytic	$47\mu$ F	10WV				
C10	CE04W1H010	Electrolytic	1μF	50WV				
C11	CQ92M1H103K	Mylar	$0.01 \mu F$	±10%				
C12	CQ92M1H393K	Mylar	0 039µF	±10%				
C13	CK45B1H102K	Ceramic	$0.001 \mu F$	±10%				
C14	CC45UJ1H02OC	Ceramic	2pF	±0.25pF				
C15	CC45TH1H100D	Ceramic	10pF	±0.5pF				
C16,17	CC45SL1H221J	Ceramic	220pF	±10%				
C18	CK45F1H103Z	Ceramic	0 01μF	+8020%				
C19	CC45CH1H15Q	Ceramic	15pF	±5%				
C20	CK45F1H103Z	Ceramic	$0.01 \mu F$	+80, -20%				
C21	CC45SL1H101J	Ceramic	100pF	±5%				
C22	CK45F1H103Z	Ceramic	0.01µF	+80, -20%				
C23~25	CC45CH1H33OJ	Ceramic	33pF	±5%				
C26,27	CK45F1H103Z	Ceramic	0 01μF	+ <b>8</b> 0, <b>- 2</b> 0%				
C28,29	CC45TH1H150J	Ceramic	15pF	±5%				
C30	CK45F1H103Z	Ceramic	0.01µF	+80,-20%				
C31	CK45B1H102K	Ceramic	0.001µF	±10%				
C32	CE04W1C100	Electrolytic	10μF	16WV				
C33	CC45CH1H05OC	Ceramic	5pF	±0 25pF				
C34	CC45TH1H080D	Ceramic	8pF	±0.5pF				
C35	CC45CH1HOR5C	Ceramic	0 5pF	±0.25pF				
C36	CC45TH1H12OJ	Ceramic	12pF	±5%				
C37	CC45CH1HOR5C	Ceramic	0 5pF	±0.25pF				

Ref No	Parts No		Description	·n	Re- marks
C38	CC45TH1H120J	Ceramic	12pF	± 5%	
C39	CC45CH1H270J	Ceramic	27pF	±5%	
C40	CK45F1H103Z	Ceramic	0 01μF	+80, -20%	
C41	CK45B1H102K	Ceramic	0 001μF	±10%	
C42 C43	CK45F1H103Z CK45B1H102K	Ceramic Ceramic	0.01μF 0.001μF	+80, -20% +10%	
C43	CC45CH1H070D	Ceramic	7pF	±10% ±0.5pF	
C45	CK45F1H103Z	Ceramic	0.01μF	+ 80, - 20%	
C46	CK45B1H102K	Ceramic	0 001μF	±10%	
C47	CS15E1VR47M	Tantalum	0.47μF	35WV	
C48	CE04W1C470	Electrolytic		16WV	
C49	CC45CH1H220J CE04W1A470	Ceramic Electrolytic	22pF	±5% 10WV	
C50 C51~53	CK45F1H103Z	Ceramic	0 01μF	+80%-20%	
C54	CK45B1H102K	Ceramic	0 001μF	±10%	
C55	CE04W1C101Q	Electrolytic	100μF	16WV	
C56,57	CC45SL2H070D	Ceramic	7pF	±0.5pF	
C58.59	CC45SL2H680J	Ceramic	68pF	±5%	
C60,61	CC45SL2H390J	Ceramic	39pF	±5%	
C62	CC45SL2H100J	Ceramic	10pF	±5% ±5%	
C63 C64~66	CC45SL2H180J CK45F1H103Z	Ceramic Ceramic	18pF 0.01μF	+80%-20%	
C67	CC45CH1H0R5C	Ceramic	0.5pF	±0.25pF	
C68	CC45CH1H020C	Ceramic	2pF	±0 25pF	
C69	CK45B1H102K	Ceramic	0.001µF	±10%	
C70	CK45F1H103Z	Ceramic	0 01μF	+ 80, -20%	
C71	CC45CH1H330J	Ceramic	33pF	±5%	
C72	CC45RH1H070D	Ceramic	7pF	±0.5pF	
C73 C74	CC45CH1H150H CC45CH1H050C	Ceramic	15pF	±5%	
C74	CC45CH1H220J	Ceramic Ceramic	5pF 22pF	±0 25pF ±5%	
C76	CC45RH1H070D	Ceramic	7pF	±0.5pF	
C77.78	CK45F1H103Z	Ceramic	0 01μF	+8020%	
C79,80	CK45B1H102K	Ceramic	$0.001 \mu F$	±10%	
C81,82	CM93F2A080D	Mica	8pF	±0.5pF	
C83	CC45SL1H010C	Ceramic	1pF	±0 25pF	
C84 C85	CC45CH1H220J CC45CH1H020C	Ceramic	22pF	±5%	
C86	CC45CH1H020C	Ceramic Ceramic	2pF 18pF	±0 25pF ±5%	
C87	CK45F1H103Z	Ceramic	0.01μF	+80,-20%	
C88	CK45B1H102K	Ceramic	0.001µF	±10%	
C89	CK45F1H103Z	Ceramic	0 01μF	+80, -20%	
C90	CC45CH1H050C	Ceramic	5pF	±0.25pF	
C91	C91-0405-15	Through ty		· ·	
C92 C93,94	CK45B1H221K	Ceramic	220pF 0 022μF	±10% ±10%	
C95,94	CQ92M1H223K CK45F1H103Z	Mylar ' Ceramic	0.01μF	+8020%	
C96	CK45B1H471K	Ceramic	470pF	±10%	
C97	CC45SL1H151J	Ceramic	150pF	±5%	
C98	CC45CH1H150J	Ceramic	15pF	±5%	
C99	CQ92M1H223K	Mylar	$0.022 \mu F$	±10%	
C100	CC45SL1H330J	Ceramic	33pF	±5%	
C101	CK45B1H471K	Ceramic	470pF	±10%	
C102 C103	CQ92M1H103K CK45B1H471K	Mylar Ceramic	0 01μF 470pF	±10% ±10%	
	CQ92M1H223K	Mylar	0 022μF	±10%	
C106	CK45B1H471K	Ceramic	470pF	±10%	
C107	CK45F1H103Z	Ceramic	0.01μF	+8020%	
C108	CQ92M1H153K	Mylar	$0.015 \mu F$	±10%	
C109	CC45CH1H470J	Ceramic	47pF	±5%	
C110.111		Ceramic	470pF	±10%	
C112	CQ92M1H472K CK45B1H471K	Mylar	0 0047μF	±10% ±10%	
C113,114	CQ92M1H102K	Ceramic Mylar	470pF Ο 001μF	±10% ±10%	
C116	CQ92M1H473K	Mylar	0 047μF	±10%	

Ref. No	Parts No.	Description	Re- marks
24.5	0002441112227	Mylar 0.022μF ±10%	
C117	CQ92M1H223K CQ92M1H102K	Mylar $0.022\mu F \pm 10\%$	
C118	CQ92M1H102K	Mylar 0.0022μF ±10%	
C119	CQ92M1H393K	Mylar 0.039µF ±10%	
C120	CQ92M1H393K	Mylar $0.0039\mu F \pm 10\%$	
C121		Mylar 0 01 µF ± 10%	
C122	CQ92M1H103K CS15E1VOR1M	Tantalum 0 1µF 35WV	
C123	CQ92M1H333K	Mylar 0 033µF ±10%	
C124 C125	CQ92M1H332K	Mylar 0.0033μF ± 10%	
C125	CS15E1C4R7M	Tantalum 4.7μF 16WV	
C120	CE04W1H3R3	Electrolytic 3.3μF 50WV	
C127	CK45F1H103Z	Ceramic $0.01\mu F + 80, -20\%$	
C128	CQ92M1H103K	Mylar $0.01 \mu F \pm 10\%$	
C129	CQ92M1H332K	Mylar 0.0033μF ±10%	
C130	CQ92M1H273K	Mylar $0.027 \mu F \pm 10\%$	
C132	CE04W1H010	Electrolytic 1µF 50WV	
C132	CE04W1C100	Electrolytic 10μF 16WV	
C133	CE04W1A470	Electrolytic 47μF 10WV	
C134	CE04W1C100	Electrolytic 10μF 16WV	ŀ
C136	CE04W1A101	Electrolytic 100µF 10WV	
C130	CE04W1C220	Electrolytic 22µF 16WV	
	CK45F1H103Z	Ceramic $0.01\mu F + 80 20\%$	
C130.13	CE04W1C220	Electrolytic 22μF 16WV	
C141	CK45F1H103Z	Ceramic $0.01\mu F + 80, -20\%$	
C142	CE04W1C100	Electrolytic 10µF 16WV	
C143	CE04W1A470	Electrolytic 47µF 10WV	
C144	CK45F1H103Z	Ceramic $0.01\mu F + 80\% - 20\%$	
C145	C91-0405-15	Through type cap. 0.001μF	
	7 CK45F1H103Z	Ceramic $0.01\mu F + 80\% - 20\%$	
C148	CE04W1C220	Electrolytic 22μF 16WV	
C149	CK45F1H103Z	Ceramic $0.01 \mu F + 80, -20\%$	
C150,15	1 CC45TH1H02OC	Ceramic 2pF ±0.25pF	
C155	CC45TH1H02OC	Ceramic 2pF ±0.25pF	
C156,15	7 CC45F1H103Z	Ceramic 0.01μF +80% - 20%	
		MICONDUCTOR  IC TA7061AP	т
Q1	V03-0039-05		1
02.3	V03-0079-05	Transistor 2SC460 (B)	ļ
Ω4,5	V09-0012-05	FET 2SK19 (GR) FET 3SK74 (L)	
Q6	V09-1002-56	117	
Q7	V03-2538-06	Transistor	1
Q8.9	V09-1002-56	Transistor 2SC460 (B)	
	7 V03-0079-05	Transistor 2SC1815 (Y)	
Q18~2		Transistor 2SC496 (Y)	
Q23,24	i .	Transistor 2SA1015 (Y)	
Q25	V01-1015-06 V03-1959-06	Transistor 2SC1959 (Y)	
027	V03-1959-06 V03-1815-06	Transistor 2SC1815(Y)	
Q28,29	V03-1815-06 V01-0113-05	Transistor 2SA496(Y)	
		Varicap diode 1S2208	
D1~5	V11-0317-05 V11-0076-05	Diode 1S1555	
D6	V11-5260-16	Diode MI402	
D8	V11-0414-05	Diode 1S2588	
D8 D9.11.1		Diode 1N60	
D3,11,1	V11-0374-05	Diode 1SS16	
	6 V11-0076-05	Diode 1S1555	
	0 V11-0051-05	Diode 1N60	
D21	V11-0076-05	Diode 1S1555	
D22	V11-1262-06	Varistor 1S1212	
D23	V11-4163-56	Zener diode XZ-088	
D24	V11-0076-05	Diode 1S1555	
D25	V11-0247-05	Zener diode WZ-100	
D26	V11-0076-05	Diode 1S1555	
D27	V11-4161-86	Zener diode XZ-064	☆
1027			

Ref No	Parts No	Description	Re- mark
	V11 0076 0F	Diode 1S1555	
D28 D29	V11-0076-05 V13-0004-05	SCR CR02AM-2-1	☆
D29 D31,32	V11-0076-05	Diode 1S1555	"
U31,32	V11-0070-03	Blode	
	Į į	POTENTIOMETER	<del>                                   </del>
VR1,2	R12-1404-05	Potentiometer 4.7kΩ	
VR3,4	R12-0406-05	Potentiometer 470Ω	
VR5	R12-0409-05	Potentiometer 220 $\Omega$	
VR6	R12-5403-05	Potentiometer 100kΩ	
VR7	R12-4404-05	Potentiometer 68kΩ	Ì
VR8	R12-1404-05	Potentiometer 4.7kΩ	
		TRIMMER	
TC1	C05-0062-05	Ceramic trimmer 6pF	
TC2	C05-0013-15	Ceramic trimmer 20pF	
		UCTOR/CRYSTALQUARTZ	
L1	L40-1021-03 L40-1545-06	Ferri inductor 1mH Ferri inductor 150mH	
L2 L3	L40-1545-06	Quartz crystal (10.7 MHz)	Ì
L4	L33-0615-05	Choke coil 15µH	
L5	L30-0005-05	IFT FOR THE SECOND STATE OF THE SECOND SECON	
L6	L31-0313-05	IFT	
L7	L40-3391-03	Ferri inductor 3.3 µH	
L8	L40-1021-03	Ferri inductor 1 mH	
L9	L31-0344-05	Tuning coil	
L10	L31-0180-05	Tuning coil	
L11,12	L31-0267-05	Tuning coil	
L13	L34-0672-05	Tuning coil	
L14	L40-1021-03	Ferri inductor 1 mH	
L15	L34-0499-05	VHF coil 3φ4T	
L16	L34-0452-05	VHF coil 3φ6T	
L17	L40-1001-03	Fern inductor 10μH	
L18	L30-0504-05	IFT	
L19	L34-0823-05	VHF coil 5ø3T	
L20	L33-0025-05	Choke coil 1µH	
L21	L34-0823-05	VHF coil 5φ3T	
L22	L30-0503-05	IFT VHF coil 3φ4T	
L23	L34-0499-05	Ceramic discri 455D	
L24 L25	L79-0442-05 L40-6825-04	Fern inductor 6.8 mH	
L25 L26	L33-0026-05	Choke coil 1µH	
L27	L34-0818-05	VHF coil 5φ4T	
L27	L33-0025-05	Choke coil 1µH	
L29,30	L34-0694-05	Tuning coil	
L31	L34-0812-05	Tuning coil	
L32	L79-0451-05	Helical block	
L33	L34-0812-05	Tuning coil	
L34	L34-0683-05	Tuning coil	
L35	L30-0289-05	IFT	
L36	L71-0201-05	Monolithic filter 10F15A	
L37	L30-0289-05	IFT	
L38	L72-0014-05	Ceramic filter SFE-10.7 MA5	
L39	L77-0327-06	Quartz crystal (10.245 MHz)	
L40	L40-1021-03	Ferri inductor 1 mH	
L41	L72-0309-05	Ceramic filter CFT-455F2	
	Λ	MISCELLANEOUS	
	E23-0046-04	Terminal (square) × 17	
D1 1	E23-0401-05 S51-1404-05	Terminal (circle) Relay	
RL1	351-1404-05	itelay	

#### PLL Unit (X50-1580-10)

Ref. No.	Parts No.		Descriptio	n	Re- marks
		CAPACITOR			1
C1~6	CK45F1H103Z	Ceramic	0.01μF	+8020%	
C7~12	CK45B1H102K	Ceramic	$0.001 \mu F$	±10%	
C13	CC45CH1H100D	Ceramic	10pF	±0.5pF	
C14	CC45CH1H27OJ	Ceramic	27pF	±0.5%	
C15	CC45UJ1H18OJ	Ceramic	18pF	±5%	
C16	CK45F1H103Z	Ceramic	$0.01 \mu F$	+80,-20%	ŀ
C17	CE04W1A470	Electrolytic	<b>4</b> 7μF	10WV	
C18,19	CC45CH1H050C	Ceramic	5pF	±0.25pF	
C20	CE04W1A470	Electrolytic	· ·	10WV	
C23	CE04W1C101Q	Electrolytic		16WV	
C24~26	CK45F1H103Z	Ceramic	0.01μF	+80,-20%	
C27	CC45CH1H33OJ	Ceramic	33pF	±5%	
C28	CC45CH1H05OC	Ceramic	5pF	±0.25pF	
C29	CE04W1H010	Electrolytic	-	50WV +80, -20%	
C30	CK45F1H103Z	Ceramic	0.01μF		1
C31	CC45CH1H100D	Ceramic	10pF	±0.5pF +80, -20%	
C32~35	CK45F1H103Z	Ceramic Ceramic	0.01μF	±0.25pF	
C36 C37	CC45CH1H050C CK45F1H103Z	Ceramic	5pF 0.01μF	+80, -20%	
C37	CS15E1C4R7M	Tantalum	4.7μF	16WV	1
C39	CS15E1C4R7M	Tantalum	4.7μ1 10μF	10WV	
C40	CC45CH1H050C	Ceramic	5pF	±0.25pF	
C40	CC45CH1H270J	Ceramic	27pF	±0.5%	
C42	CC45CH1H39OJ	Ceramic	39pF	±5%	
C43~53	CK45F1H103Z	Ceramic	0.01μF	+80,-20%	ļ.
C54	CE04W1E4R7	Electrolytic	4.7μF	25WV	
C55	C90-0246-05	Ceramic	0.01µF	±10%	
C56	CE04W1C100	Electrolytic	10µF	16WV	
C57	CK45F1H103Z	Ceramic	$0.01 \mu F$	+80,-20%	
C58	CC45SL1H101J	Ceramic	100pF	±5%	
C59	CK45F1H103Z	Ceramic	$0.01 \mu F$	+80,-20%	
C60	CC45CH1H100D	Ceramic	10pF	±0.5pF	
C61	CC45CH1H330J	Ceramic	33pF	±5%	
C62	CE04W1A470	Electrolytic		10W,V	
C63,64	CK45F1H103Z	Ceramic	0.01μF	+8020%	
C65,66	CQ92M1H332K	Mylar	0.0033μF		
C67	CQ92M1H103K	Mylar.	0.01μF	±10%	
C68	CQ92M1H472K CE04W1H010	Mylar	0.0047μF 1μF	50WV	
C69	CQ92M1H332K	Electrolytic Mylar	0.0033μF		
C70	CE04W1A101Q	Electrolytic		10WV	
C71	CQ92M1H102K	Mylar	0.001μF	±10%	
C72	CK45B1H331K	Ceramic	330pF	±10%	
C74	CQ92M1H472K	Mylar	0.0047µF		
C75	CE04W1C101Q	Electrolytic		16WV	j
C76	CE04W1C100	Electrolytic		16WV	
C77	CE04W1A330	Electrolytic		10WV	
C78	CQ92M1H393K	Mylar	0.039µF	±10%	
C79	CE04W1A330	Electrolytic	33µF	10WV	
C80	CE04W1A101Q	Electrolytic	100μF	10WV	
C81	CQ92M1H104K	Mylar	O.1μF	±10%	
C82	CE04W1C471Q	Electrolytic	470μF	16WV	
C84	CE04W1A470	Electrolytic	47μF	10WV	
C85	CC45CH1H070D	Ceramic	7pF	±0.5pF	
C86	CC45CH1H150J	Ceramic	15pF	±5%	
C87	CC45CH1H030C	Ceramic	3pF	±0.25pF	
C88	CK45F1H103Z	Ceramic	0.01μF	+80,-20%	
C89	CE04W1C100	Electrolytic		16WV	
1 000	CK45B1H102K	Ceramic	0.001μF	±10%	
C90					
C91	CC45CH1H030C	Ceramic	3pF	±0.25pF	
	CC45CH1H030C CC45UJ1H020C CC45CH1H080D	Ceramic Ceramic Ceramic	3pF 2pF 8pF	±0.25pF ±0.25pF ±0.5pF	

Ref. No.	Parts No.	Description	Re- marks
C94	CQ92M1H103K	Mylar 0.01μF ±10%	
C95	CC45UJ1H060D	Ceramic 6pF ±0.5pF	
	SE	MICONDUCTOR	
Q1~5	V03-1815-06	Transistor 2SC1815 (Y)	T
Q6	V03-0079-05	Transistor 2SC460 (B)	
Q11,12	V09-1002-56	FET 3SK74 (L)	
Q13,14	V03-1815-06	Transistor 2SC1815 (Y)	
Q15	V30-1030-46	IC SM5111A	☆
Q16	V03-1815-06	Transistor 2SC1815 (Y)	
Q17	V03-0272-05	Transistor 2SC1345 (E)	
Q18	V03-1815-06	Transistor 2SC1815 (Y)	
Q19	V30-0087-05	IC TA7060P	
Q20	V03-1923-06	Transistor 2SC1923 (0)	☆
Q21,22 Q23,24	V03-1815-06 V03-2240-06	Transistor 2SC1815 (Y) Transistor 2SC2240 (GR)	
025	V30-0208-05	1 ' '	
Q26	V30-0208-05 V09-0060-05	IC AN315 FET 2SK30A (GR)	
Q27	V09-0060-05 V09-1001-16	FET 25K30A (GR) (T)	
028	V03-1001-10	Transistor 2SC1923 (0)	☆
Q29	V30-1030-26	IC μPC78L08A	^
D1~5	V11-0414-05	Diode 1S2588	
D6~10	V11-4161-36	Varicap diode 1SV53A	
D11~20	V11-0076-05	Diode 1S1555	
D21	V11-0374-05	Diode 1SS16	
D23,24	V11-0414-05	Diode 1S2588	Ì
D25	V11-4161-56	Zener diode WZ-040	☆
D26	V11-0317-05	Varicap diode 1S2208	
	PC	DTENTIOMETER	
VR1∼5	R12-5403-05	Potentiometer 100kΩ	
VR6	R12-1403-05	Potentiometer $1k\Omega$	☆
		TRIMMER	
TC1	C05-0067-05	Ceramic trimmer 25pF	
TC2	C05-0062-05	Ceramic trimmer 6pF	
	C	OIL/INDUCTOR	
L1~5	L34-0437-05	Choke coil	☆
L6	L77-0832-05	Quartz crystal 43,7667 MHz	☆
L7	L77-0833-05	Quarts crystal 44,4333 MHz	☆
L8	L77-0834-05	Quartz crystal 43,5667 MHz	☆
L9	L77-0835-05	Quartz crystal 44,2333 MHz Quartz crystal 44,6333 MHz	☆
L10	L77-0836-05		☆
L11 L12	L40-1511-03 L33-0605-05	Ferri-inductor 150µH Choke coil 0.47µH	
L12	L32-0005-05	Oscillator coil	
L14	L34-0683-05	Tuning coil	
L15	L34-0820-05	Tuning coil	☆
L16	L34-0683-05	Tuning coil	~
L17	L77-0720-05	Quartz crystal 10,240 MHz	
L18	L40-3301-03	Ferri-inductor 33µH	
L19	L40-1091-03	Ferri-inductor 1µH	
L20	L15-0016-05	Choke coil (Low frequency)	
L21	L40-1021-03	Ferri-inductor 1mH	
L22	L40-1021-25	Ferri-inductor 1mH	1
L23	L40-3391-03	Ferri-inductor 3.3μH	
L25	L32-0618-05	Oscillator coil	☆
	MI	SCELLANEOUS	···-
	555 5545 54	1	1
	E23-0046-04 E23-0401-05	Terminal × 8 (square) Terminal × 2 (circle)	

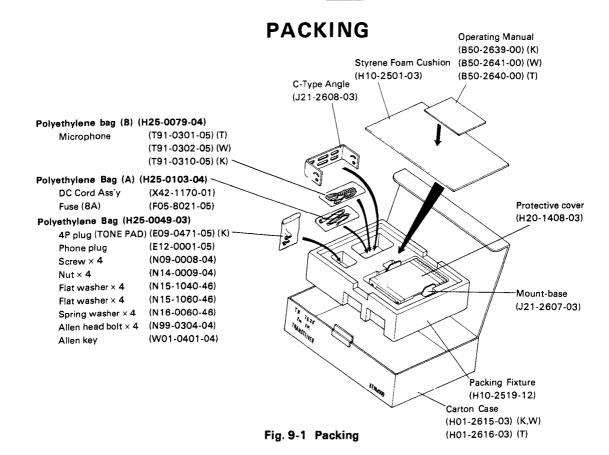
### PARTS LIST/PACKING

#### **CONTROL UNIT (X54-1440-10)**

Ref. No.	Parts No.	Description		Re- marks
		CAPACITOR		
C1	CE04W1C470Q	Electrolytic 47µF 16WV		
C2	CE04W1A470	Electrolytic 47μF 10WV	- 1	
R1,2	R90-0514-05	Resistor block 10k × 7		☆
R3∼5	R90-0516-05	Resistor network		☆
R6	R90-0515-05	Resistor block 10k × 4		☆
Ω1∼6	V03-1815-06	Transistor 2SC1815 (Y)	١	
Ω7	V01-1015-06	Transistor 2SA1015 (Y)	ļ	
IC1~3	V30-1006-46	IC TC4035BP		攻
IC4~6	V30-1049-06	IC TC4019BP	İ	
1C7∼9	V30-1054-06	IC TC5022BP		
IC10,11	V30-1006-36	IC TC4081BP		☆
IC12	V30-1025-26	IC FS7806M		☆
D1~22	V11-0051-05	Diode 1N60		
D23	V11-0076-05	Diode 1S1555	- 1	
D24	V11-0307-05	Zener diode WZ-150		
D25	V11-3162-86	LED TLG205		☆
D26	V11-3162-96	LED TLR205		☆
D27~30	V11-4161-66	LED 513 OK		☆
S1	S29-1406-05	Rotary switch (1 MHz) (	K)	☆
S-1	S29-1408-05	Rotary switch (1 MHz) (V	W)	☆
S2	S29-1405-05	Rotary switch (100 kHz, 10 kHz)		☆
S3	S40-2405-05	Push switch (Ok, 5k)		
S4	S29-4402-05	Slide rotary (for shift)		☆

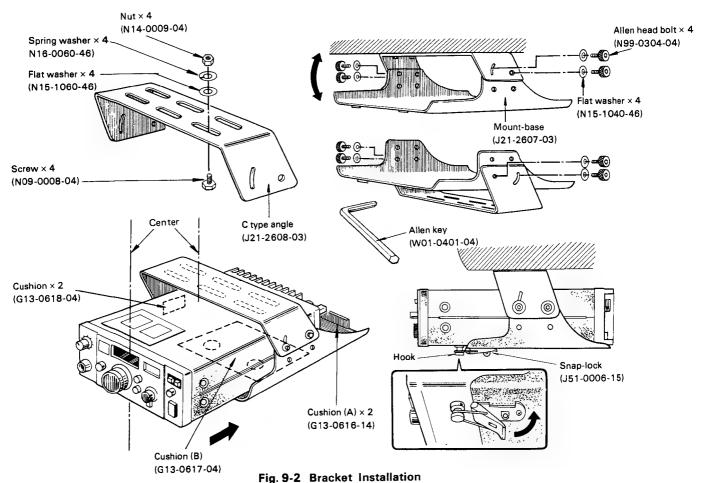
# TONE UNIT (X52-1110-50) (T TYPE) (X52-1110-61) (W TYPE)

Ref. No.	Parts No.		Description	n		Re- marks				
C1	CK45B1H102K	Ceramic	1000pF	±109	6					
C2	CE04W1C220Q	Electrolytic	22μF	16W	V					
C3~5	C91-0433-05	Layer-built	0.0039µF	±5%		☆				
С6	CE04W1C220Q	Electrolytic	22μF	16W	<b>v</b>					
C7,8	CE04W1H010	Electrolytic	1μF	50W	<b>V</b>					
C9,10	CK45B1H102K	Ceramic	1000pF	±109	6					
C11	CS15E1A150K	Tantalum	15μF	±109	6	(T)				
C12	CK45B1H102K	Ceramic	1000pF	±109	6					
C13	CS15E1A150K	Tantalum	15μF	±109	6	(T)				
	RESISTOR									
R1~12	RD14CB2EOOOJ	Carbon	ΩΟΟΟ	±5%	1/4W					
R2,3	R92-0616-05	Metal film	10kΩ	±1%	1/4W					
R4	R92-0617-05	Metal film	$7.5k\Omega$	±1%	1/4W	☆				
R5	RN14BK2E4703F	Metal film	470k $\Omega$	±1%	1/4W	☆				
R10	RD14CB2E102J	Carbon	15k $\Omega$	±5%	1/4W					
						(T)				
	SEN	VICONDUC.	TOR							
Q1,2	V03-0093-05	Transistor 2	SC458 (B)							
D1,2	V11-0076-05	Diode 1	S1555			(T)				
D1	V11-0076-05	Diode 1	S1555			(W)				
	PO	TENTIOME	ΓER			f				
VR1	R12-2405-05	Semi-fixed	resistor 5kΩ			☆				
VR2	R12-4403-05	Semi-fixed	resistor 50k	Ω		(T) ☆				
	MI	SCELLANEC	us							
	E40-0464-05	Pin plug	4P							
	L									

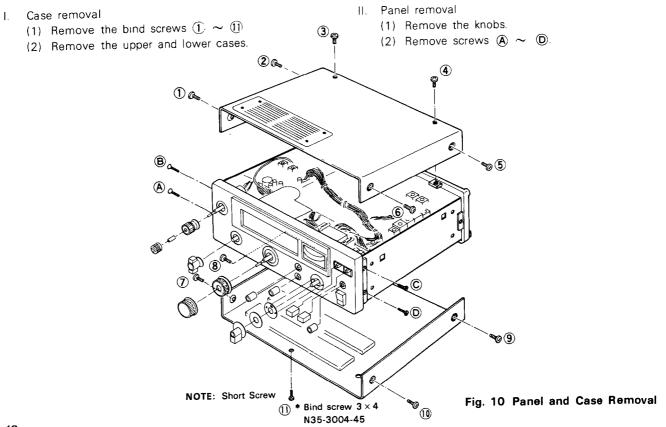


# TR-7625

# BRACKET INSTALLATION/EXPLODED VIEWS



**EXPLODED VIEW** 



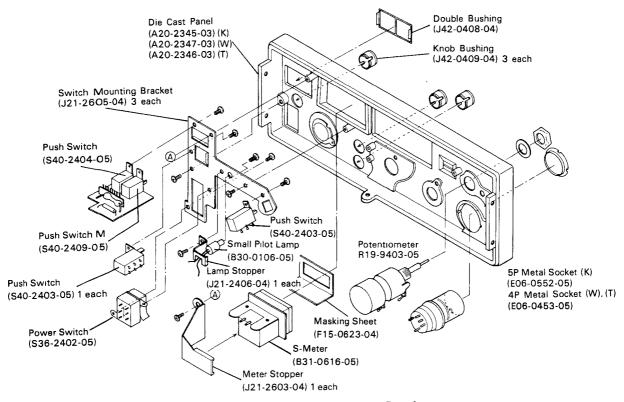
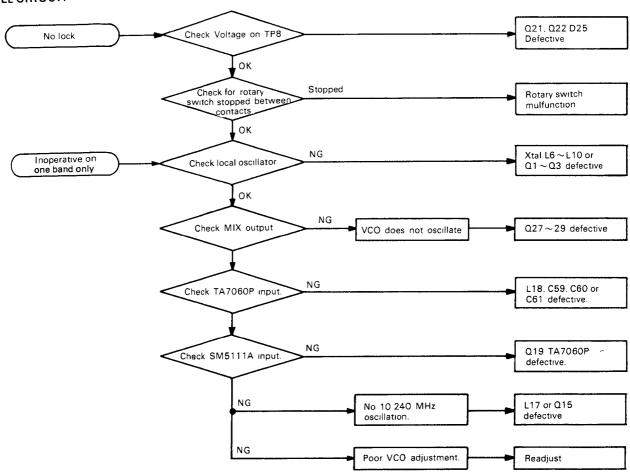


Fig. 11 Disassembly of Front Panel

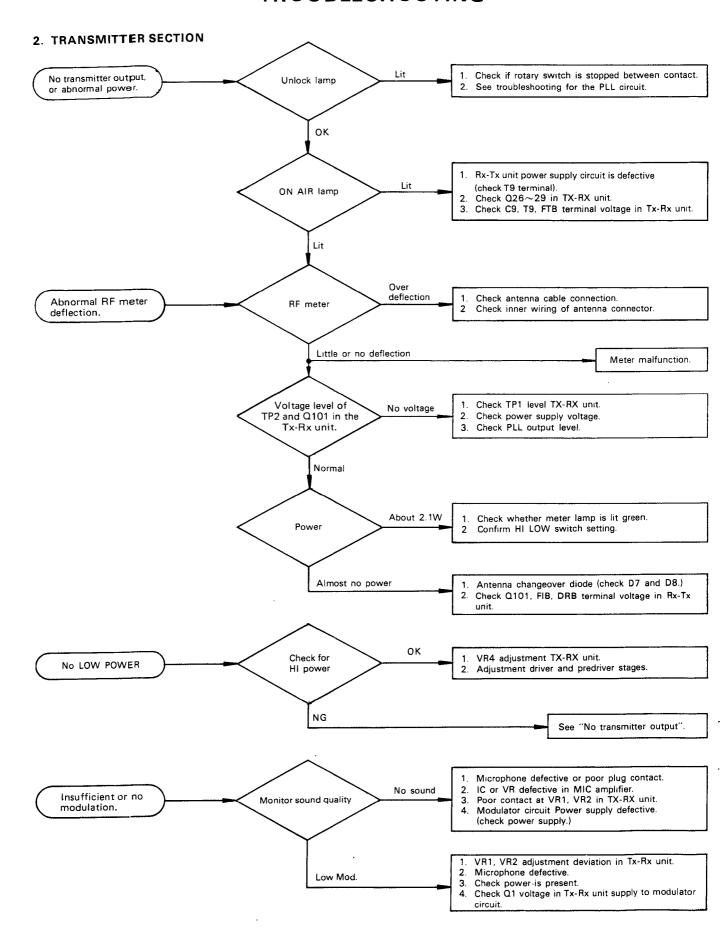
#### **TROUBLESHOOTING**

#### 1. PLL CIRCUIT

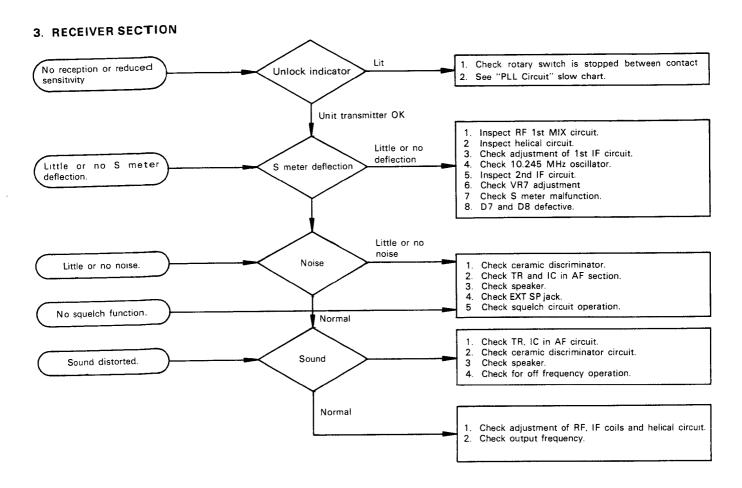


# TR-7625

#### **TROUBLESHOOTING**



# TROUBLESHOOTING/ADJUSTMENTS



#### **ADJUSTMENTS**

#### TEST EQUIPMENT REQUIRED

1. DC Power Supply

Voltage:

Variable from 9 to 16V.

Current:

8A min.

2 DC VTVM or DVM

Voltage range:

10V~16V (min.)

Input impedance:

1 M $\Omega$  or better

3 RFVTVM

Voltage range:

F.S.  $10 \text{ mV} \sim 300 \text{V}$ 

Frequency response:

200 MHz min.

Input impedance:

1 MΩ min., 3pF max.

4. Frequency Counter

Frequency response:

150 MHz min.

Min. input sensitivity:

about 50 mV

Input impedance

1 M $\Omega$  min.

5. Oscilloscope

With horizontal input and high sensitivity.

Frequency response:

3 MHz min.

6. Power Meter with Dummy Lead

Frequency limit:

150 MHz min.

Impedance:

Ranges:

50W, 3W

 $50\Omega$ 

#### 7. Linear Detector

8. Audio Generator (AG)

Frequency range:

 $300 \, \text{Hz} \sim 5 \, \text{kHz}$ 

Output:

 $0.5 \text{ mV} \sim 1 \text{V}$ 

9. AF Voltmeter

Frequency range:

50 Hz ~ 10 kHz Input impedance:

1 M $\Omega$  min.

Voltage range:

 $3 \text{ mV} \sim 30 \text{V}$ 

10. Standard Signal Generator (SSG)

Output frequency:

Capable of covering 144 MHz

 $\sim$  148 MHz

Modulation:

Frequency modulation

11. Sweep Generator

Frequency range:

Capable of covering 144 MHz

 $\sim$  148 MHz

12. AF Dummy Load

8 $\Omega$  5W (approx.)

13. Directional Coupler

14. Detector Probe

# TR-7625

#### **ADJUSTMENTS**

# 1. PLL Adjustments (See Fig. 1 on page 28 for Set-up)

lto	Condition	Meas	uring po	oint			Adjust	Reference	Remarks		
Item	Condition	Instrument	Unit	Terminal	Unit	Parts	Method	Hererence	Nemarks		
Voltage check and ad- justment	1) POWER SW: ON HI LOW SW: HI MR SW: OFF MODE SW: S		PLL	T9 (J1)				8 9V ~ 10 2V			
initial control setting	MHz SW: 6 100 kHz SW: 0 10 kHz SW: 0 SUBTONE SW: 0 5Hz SW: 0	DC VTVM	TX RX	Т9				8 9V ~ 10 2V	Confirm		
	REMOTE SW: OFF SEND/REC. SEND			СВ				Approx 12V			
	2) SEND/REC. REC.	-	TX RX	R9		·		7 7V ~ 8 3V			
	3) Same as above.		PLL	TP3	PLL			Approx 8 OV			
	4) Same as item 2)		PLL	TP8	PLL	VR6	6 OV	±0.2V			
2 PLL	1) 100 kHz SW: 0 10 kHz SW: 0	RF VTVM	PLL	TP1	PLL	L13	Turn the L13 core counter clockwise 180° from oscil- lation starting point	0 46V			
				TP7	1	L14	MAX	1 4V			
	2) MHz SW: 4	DC VTVM	PLL	TP5	PLL	TC2	1 5V	±0.05V			
	3) MHz SW: 7 100 kHz SW: 9	DC VTVM	PLL	TP5				Less than 5 5V	Confirm		
	10 kHz SW: 9			TDC		TC1	10.24000 -1-	10011-			
	4) Same as above 5) MHz SW: 4	F Counter	PLL	TP6	PLL	TC1	10 24000 Hz	±100Hz			
	100 kHz SW: 0 10 kHz SW: 0 5 kHz SW: 5 kHz					L1	133 3050 MHz	+ 500 Hz			
	6) MHz SW: 6					L2	135 3050 MHz	± 500 Hz			
	7) MHz SW: 5  MODE SW: ⊕  SEND/REC SW: SEND	Frequency Counter	Counter	Counter	PLL	TP4	PLL	L3	133 7050 MHz	±500 Hz	
	8) MHz SW; 7					L4	135 7050 MHz	± 500 Hz			
	9) MODE SW: €				ļ	L5	136 9050 MHz	± 500 Hz			
	10) MHz SW: 4 5 kHz SW: 0 MODE SW: S SEND/ REC REC					VR1	133 3000 MHz	±500 Hz			
	11) MHz SW: 6	F COUNTER	PLL	TP4	PLL	VR2	135 3000 MHz	±500 Hz			
	12) MHz SW: 5 MODE SW: ⊖ SEND/REC. SNED					VR3	133 7000 MHz	±500 Hz			
	13) MHz SW: 7					VR4	135 7000 MHz	±500 Hz	-		
	14) MODE SW: ⊕ Recneck the frequencies in Item (5) through (9) If they are deviated, readjust					VR5	136 9000 MHz	±500 Hz			
	L1 through L5 necessary										
	15) MHz SW: 5 100 kHz SW: 9 10 kHz SW: 9 MODE SW: S SEND/REC REC	F Counter	PLL	TP4				135 2900 MHz ± <b>500 Hz</b>			
	17) MHz SW: 5 MODE SW: ⊖ SEND/REC SEND 18) MHz SW: 7	r Counter	. Sounter	Counter						±500 Hz 134 6900 MHz ±500 Hz 136 6900 MHz ±500 Hz	
	19) MHz SW: 4 100 kHz SW: 0 10 kHz SW: 0						,	132 7000 MHz <b>±500 Hz</b>			

	Q , disi	Meas	uring po	oint			Adjust	- Reference	Remarks
Item	Condition	instrument	Unit	Terminal	Unit	Parts	Method		
- Di i	20) MHz SW 6	Frequency	PLL	TP4				134 7000 MHz ±500 Hz	
PLL (Cont )	21) MHz SW 5 SEND/REC. REC	Counter						134 3000 MHz ±500 Hz	
	22) MHz SW 7							136 3000 MHz ± 500 Hz	
	23) MHz SW 6 SEND/REC.SW. SEND							135 9000 MHz ± <b>500 Hz</b>	
1:	MODE SW ①  24) MHz SW 7  SEND/REC. REC							136 3000 MHz ± 500 Hz	
	25) MHz SW 4 SEND/REC SW SEND							133 3000 MHz ±500 Hz	
	& REC 26) MHz SW 5 SEND/REC. SEND							134 3000 MHz ± <b>500</b> Hz	
- - -	& REC  27) MH <sub>2</sub> SW 4→5→6→7→4  MODE SW S  SEND/REC REC		PLL	TP4				The frequency should become higher than 133 3000 MHz in 1 MHz steps and should re-	
		F Counter						turn to the original frequency at the "4" position	
	28) 100 kHz SW 0 +1 + 9 → 0							The frequency should become higher than 133 3000 MHz in 100 kHz steps and should return to the original frequency at the "O" position	
	29) 10 kHz SW 0 → 1 → 9 → 0							The frequency should become higher than 133 3000 MHz in 10 kHz steps and should re- turn to the original frequency at the "0" position	
	30) MHz SW 6 SEND/REC SW SEND	RF VTVM	PLL	ТР4	PLL	L15	MAX		
3 Wax se all coil adjust men	al 1) L1 L2 L3 L4 L5 ht L13								

#### 2. TX Adjustments (See Fig. 2a-d on page 28, 29 for Set-up)

Item	Condition	Meas	uring po	oint	<u> </u>		Adjust	Reference	Remarks	
		instrument	Unit	Terminal	Unit	Parts	Method	Hoterenee	Hemaiks	
1 Initial control setting HI/LOW SW HI MR SW OFF MODE SW S MHz SW 4 100 kHz SW 0 5 kHz SW 0 5 kHz SW 0 SUBTONE SW OFF REMOTE SW OFF SEND/REC SEND TC 1 Centered TC 2 Centered WPS Counter	HI/LOW SW HI MR SW OFF MODE SW S MHz SW 4 100 kHz SW 0 10 kHz SW 0 5 kHz SW 0 SUBTONE SW OFF REMOTE SW OFF SEND/REC SEND TC 1 Centered TC 2 Centered VR8 Counter							0 4 V	Key only during actual adjustment period	
2 10 7	clockwise (CCW)	RF VTVM	TX RX	TP1	TX RX	L5 L6	MAX	0.41/		
2 .10 7 MHz		F Counter	TX RX	TP1	TX RX	TC1	10 7000 MHz	±50 Hz		
3 VCT	11 MHz SW 4 → 5 · 6 → 7	DC VTVM	TX RX	TP3				Check voltage goes up step by step	Confirm	
4 B P F DRIVE	1) MHz ŚW 6		TX RX	gate 1 of Q6	TX RX	L9 10 L11 VR3	MAX Repeat procedure two or three times	1 2V (R M S)	Adjust for peak	
	2) MHz SW 7 100 kHz SW 9 10 kHz SW 9	RF VTVM	TX RX	TP2	TX RX	L12. 13	MAX Repeat procedure two or three times			
	3) MHz SW 4 100 kHz SW 0 10 kHz SW 0		TX RX	RFI	TX RX	L13	MAX			
5 RF POWER	1) MHz SW 4 100 kHz SW 0 10 kHz SW 0 POWER SW ON	DC A M			TX RX	L13	MAX			
	2) MHz SW: 6 100 kHz SW 0 10k Hz SW 0	POWER M DC A M	Rea	r panel	TX RX	TC2 L21	Adjust TC2, L21 for Max.	Less than 6 0A More than 25W	If RF output is less than 25W, adjust L21 spacing and TC2 for best effici- ency at rated output.	
	3) Same as above	POWER M DC A M	Ant	Term	TX RX	L101	Adjust L101 to increase to inductance	Less than 6A		
	4) MHz SW 4	POWER M DC A M						More than 25W Less than 6A	Confirm	
	5) MHz SW 7 100 kHz SW 9 10 kHz <b>SW</b> :9	POWER M DC A M						More than 25W Less than 6A	Confirm	
6 RF METER	1) MHz SW 6 100 kHz SW 0 10 kHz SW 0 TX RX unit VR6 Centered	RF METER	front panel		TX RX	VR6	Meter indicates "8"			
7 LOW POWER	1) HI/LOW SW LOW	POWER M			TX RX	VR4	5.0W	Check that the meter lamp changes from yellow to green in low power		
	2) MHz SW 4	POWER M						3~7W		
	3) MHz SW 7 100 kHz SW 9 10 kHz SW 9	POWER M	rear pa					3~7W	Confirm	

	Condition	Meas	uring po	int			Adjust	Reference	Remarks
Item	Condition	Instrument	Unit	Terminal	Unit	Parts	Method		
8 RF Output at 11.5V DC input	1) DC Terminal 11 5 V 2) MHz SW 6 10 kHz SW 0 100 kHz SW 0 3) MHz SW 4	POWER METER	rear ( ANT	oanel Term				Check power output	Confirm
	4) HI/LOW SW HI 5) MHz SW 6 6) MHz SW 7 100 kHz SW 9 10 kHz SW 9							More than 15W	
9 Frequency check	1) DC input 13 8V 2) MHz SW 6 100 kHz SW 0	F Counter			TX RX	TC1	146 000 MHz	±200 Hz	
10 Protection	10 kHz SW 0  1) Connect the Power  Meter to the ANTENNA	DC VTVM	TX RX	TP4	TX RX	VR5	MIN (Null) (146 00 MHz)		
	2) Disconnect the Power meter and lead from the ANTENNA TX.RX unit VR8 VR8 Full counter-clockwise Antenna shorted to ground	DC A.M			TX RX	VR8	3 0A (144 00 MHz)		in antenna shorted to ground, adjust to relay still turning point
	3) MHz SW 4							Approx 30A	Confirm
	4) MHz SW 7 100 kHz SW 9 10 kHz SW 9							Approx 3.0A	Confirm
	5) Connect the power meter to the ANTENNA	POWER M	rear panel	ANT TERM				RF output to spec.	Confirm
11 Deviation		Linear Detector			TX RX	VR2	5 O kHz DEV		
	2) AG OUTPUT 3 mV/	Linear Detector			TX RX	VR1	35 kHz DEV		
12 SUBTON	E 1) MIC Terminal OPEN SEND/REC SEND AG OUTPUT 300 mV/ 1 kHz SUBTONE SW ON	/ Linear Detector		SUB GND > AG TB DC VTVM				1) Check that output waveform from the Linear Detector 2) Confirm that TV Terminal Voltage is approx 10V	AG output applied to SUB and GND terminal.
13 Abnorma Oscillat- ion	1) Same as above 2) HI/LOW SW LOW 3) MHz SW 4 4) HI/LOW SW HI 5) MHz SW 7 100 kHz SW 9 10 kHz SW 9 6) HI/LOW SW LOW	Linear Detector						Vary the supply voltage from 11.5 to 16 V for each item to check for abnormal oscillation or operation	
14 Shift & Memory Shift	1) MHz SW 5 100 kHz SW 0 10 kHz SW 0 5 kHz SW 0 HI/LOW SW HI 13.8V DC MODE SW © SEND/REC SW SENI	F. Counter	rear panel	ANT TERM.			,	144 400 MHz	Confirm
	MR SW OFF  2) MODE SW							145 000 MHz	Confirm
	3) MHz SW 7 MODE SW ⊝							146 400 MHz	Confirm
	4) MODE SW ⊕							147 600 MHz	Confirm
	5) MODE SW S M SW (NON-LOCK) ON								

	Item Condition	Measuring point			Adjust			Reference	Remarks
ttem Condition	Instrument	Unit	Terminal	Unit	Parts	Method	Melerence	Nemarks	
Shift and memory shift	6) MHz SW 4 MODE SW M (green)	F. Counter	rear panel	ANT TERM				147 000 MHz Check that LED's Indicate "7 000"	Confirm
(cont)	7) MODE SW S							144 000 MHz	Confirm
	8) MR SW ON							147 000 MHz Check that LED's Indicate "7,000"	Confirm
5 Wax seal all coil adjust- ment	1) L10, L11, L12, L13								

# 3. RX Adjustment (See Fig. 3a-b on page 29 for Set-up)

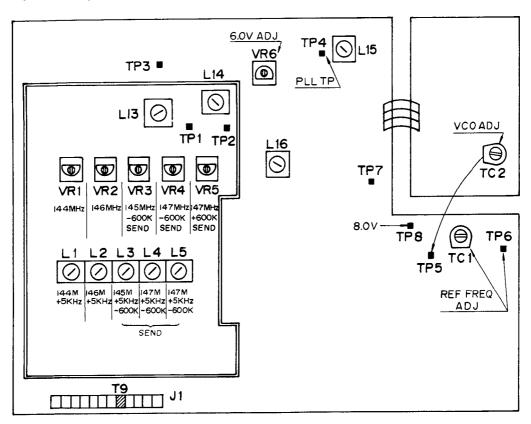
	Condition	Measuring point			Adjus			Reference	<b>D</b>	
item		instruments	Unit	Terminal	Unit	Parts	Method	neierence	Remarks	
Initial controi SETTING	1) POWER SW ON HI, LOW SW LOW MR SW OFF MODE SW S MHz SW 5 100 kHz SW 9 10 kHz SW 5 5 kHz SW 0 SUBTONE SW OFF REMOTE SW ON SEND/REC REC SQUELCH VR MIN EXT. SP terminal: AF VTVM, 8Ω Oscilloscope									
2 Helical block	1) ANT terminal SWEEP GEN Oscilloscope VERT GAIN MAX	Oscillo scope (Detector)	TX RX	TP5	TX RX	L29,30 L31 L32 (abc) L33	Adjust for a maximum gain and for a waveform as shown at right	MHz MHz MHz 1475	Repeat	
CAUTION: Do not attempt adjust-										
ment without a Sweep Generator							Adjust L29 and L30 for a maximum waveform Adjust L31 L32 (a b c)	Readjust L29 and L30 if the waveform is distorted as shown		
							and L33 for proper bandwidth and optimum waveform	below.		
3. IF GAIN	ANT. SSG (DEV 5 kHz MOD						Adjust SSG for correct frequency and optimum waveform			
	1 KHz SSG OUTPUT Approx. 10dB (2μV) AF GAIN: 0.63V/8Ω	AF VTVM								
	2) SSG OUTPUT 5~10 dE	S METER			TX RX	L34.35	MAX Repeat procedure two or three times			
4 S METER	1) SSG OUTPUT 30 dB	S METER			TX RX	VR7	Set scale 30μV	30 dB±4 dB		
5. Discrimi-	1) SSG OUTPUT OdB (0 5µV)	AF VTVM			TX RX	L22	MAX			

# ADJUSTMENTS/PC BOARD ALIGNMENT AND TEST POINT LOCATIONS

ltem	Condition	Measuring point			Adjust			Reference	Remarks
		Instrument	Unit	Terminal	Unit	Parts	Method	Troision	Tremains
6 S/N (Signal to Noise ratio)	1) SSG OUTPUT - 6 dB 2) MHz SW 4 100 kHz SW 0 10 kHz SW 0	AF VTVM						S/N 20 dB	Confirm
(6dB 0 25μV)	3) MHz SW 7 100 kHz SW 9 10 kHz SW 9						With a signal received at each channel, Set AF $\cdot$ GAIN for 0.63V/8 $\Omega$ . Next turn the SSG and	S N 20 dB	Confirm
	4) MHz SW 5 10 kHz SW 9 SSG OUTPUT 40 dB (50μV) (DEV.: 3.5 kHz)						measure the noise	S N 40 dB	Confirm
7 SQUELCH	1) SSG OUTPUT OFF SQUELCH threshold on	Oscillo- scope or speaker						Critical point 9 00 ~ 11 00	Confirm
	2) SSG OUTPUT: —6dB (0 25µV) SQUELCH threshold	,						When signal is applied squelch should open	Confirm

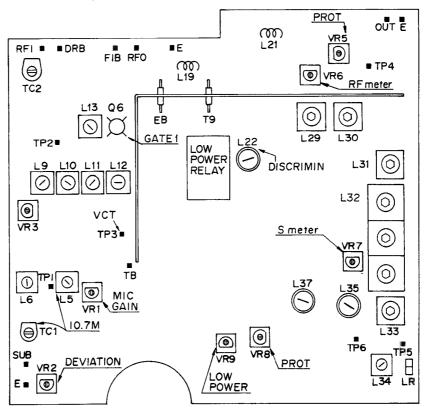
# PC BOARD ALIGNMENT AND TEST POINT LOCATIONS

#### PLL Unit (X50-1580-10)



# PC BOARD ALIGNMENT AND TEST POINT LOCATIONS

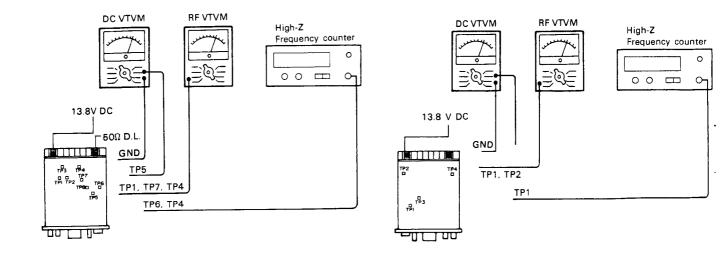
TX, RX Unit (X44-1320-10)



# **TEST AND ALIGNMENT SET-UPS**

1. PLL Adjustments Fig. 1.

Fig. 2a. TX adjustments

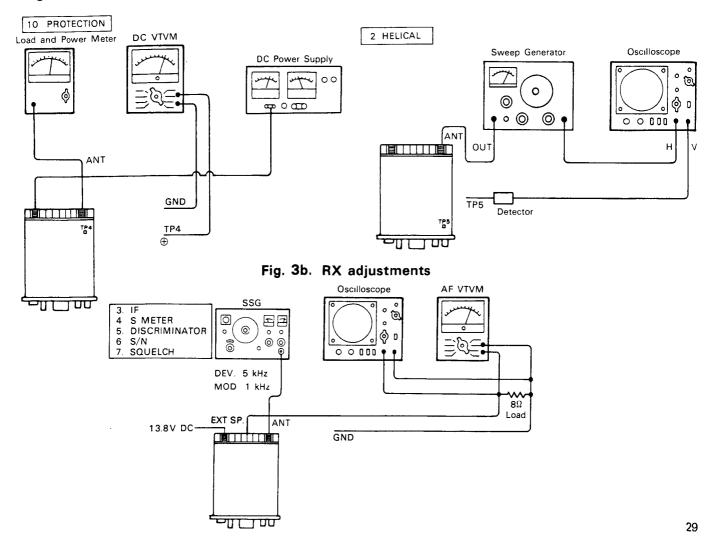


#### TEST AND ALIGNMENT SET-UPS

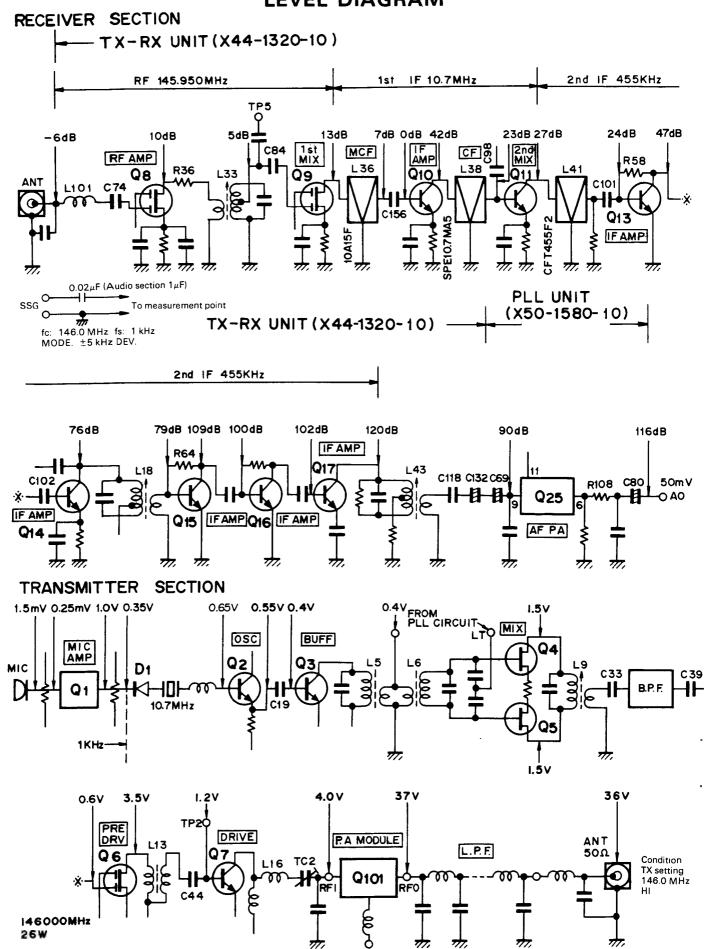
Fig. 2c. TX adjustments Fig. 2b. TX adjustments 11 DEVIATION Power Meter 12 ABNORMAL OSCILLATION DC Power Supply Frequency Counter Oscilloscope Load and Power Meter 0 00 🖽 Linear Detector DC Power Supply 0 @ 0 00 (A) D @ Ø ANT 00000  $\circ \varpi$ POWER Directional Coupler RF METER LOWER POWER <del>ஹ ப ப ம</del> 115V ANT 9. FREQ. CHECK SHIFT AND MEMORY SHIFT Audio VTVM Audio Generator 13 8V DC 0 0 ত্তি VR2 טיי 🔲 טי MIC

Fig. 2d. TX adjustments

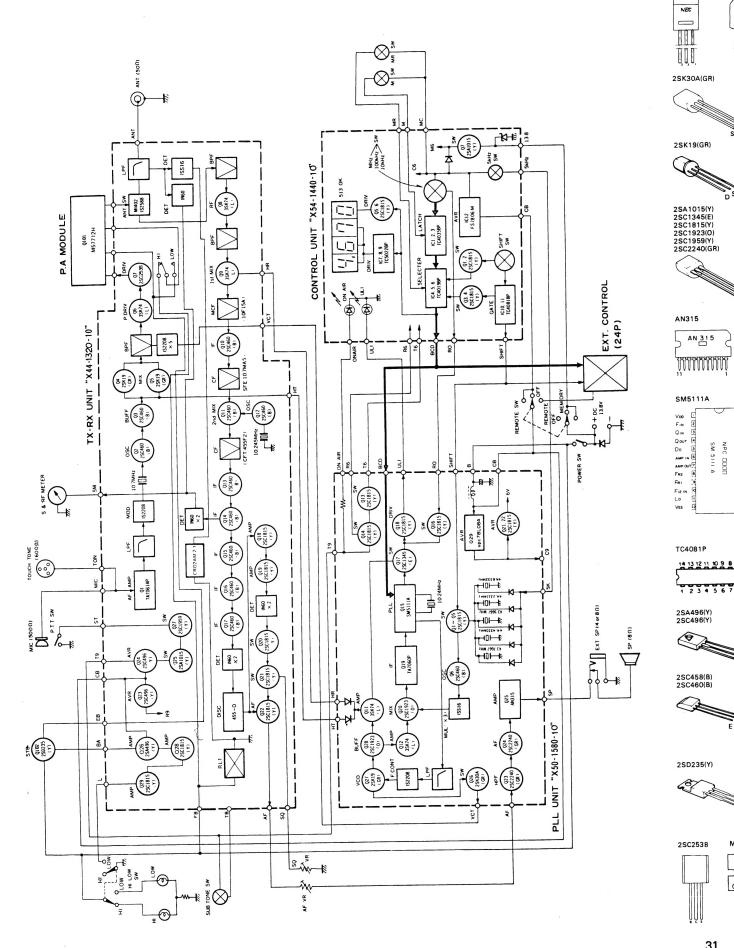
Fig. 3a. RX adjustments



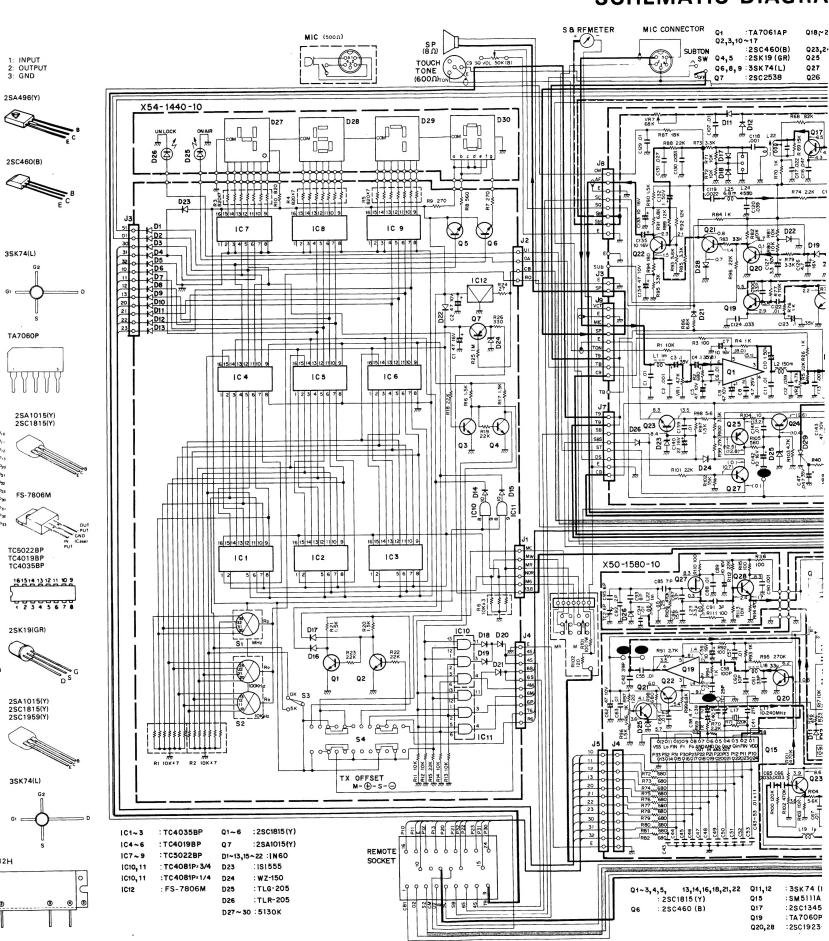
#### LEVEL DIAGRAM



# **BLOCK DIAGRAM (K)**



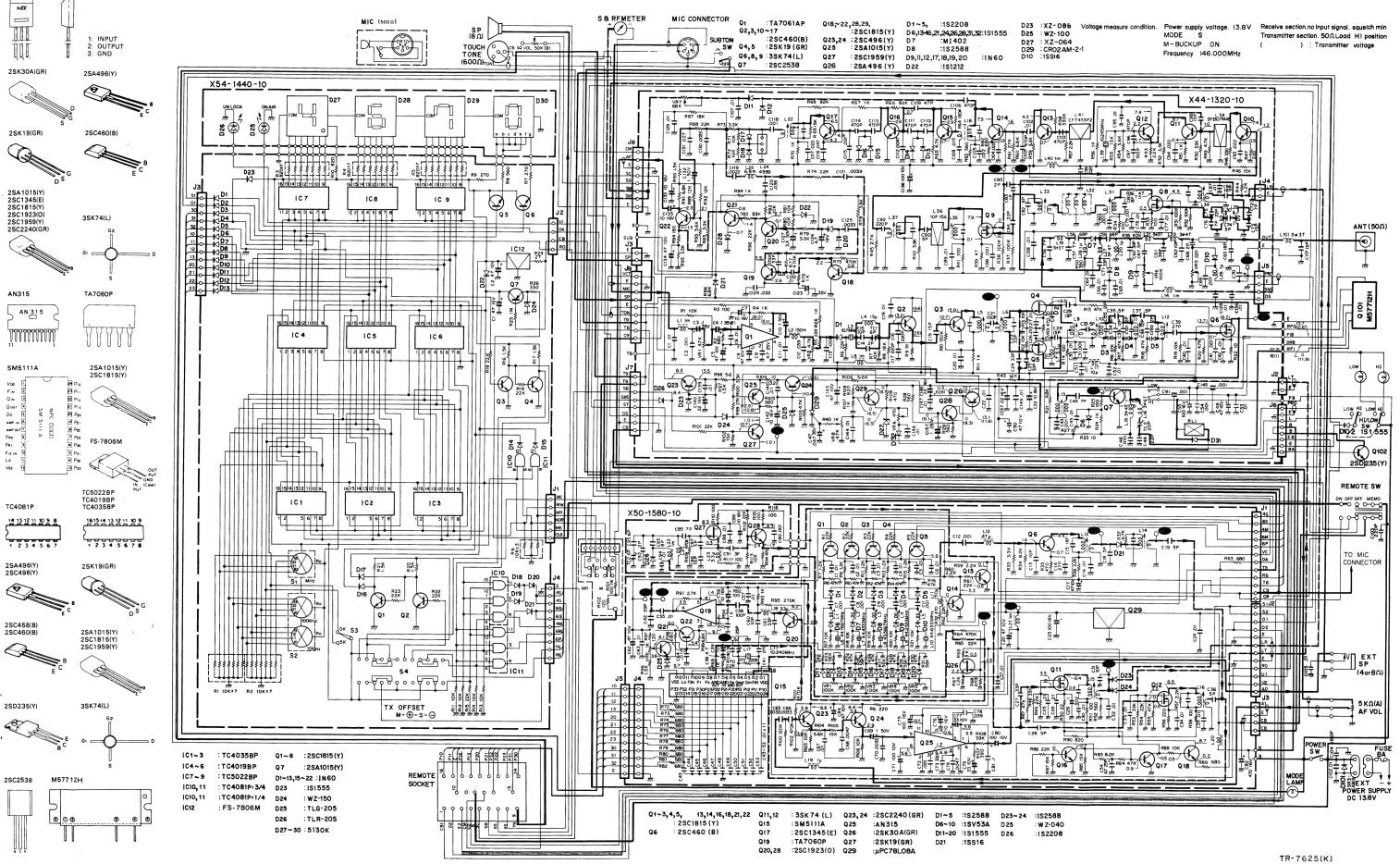
# **SCHEMATIC DIAGRA**



M57712H

μPC78L08A

# SCHEMATIC DIAGRAM (K)



µPC78L084

#### <Switch Logic>

#### Control Unit (X54-1440-10)

	J-3	5 kH:	z SW.										1
		OFF	ON									BCD.COE	)E
51	٥	1	0									BCD.COL	, .
01	0	0	1	144	MHz	145	MHz	146	MHz	147	МНz		F. order
30	0			(	)		l	(	)		1		1
31	0				l		l				l		MHz
32	0			(	)	(	)	(	)	(	) ,		200
CH. Knob-	-	0	1	2	3	4	5	6	7	8	9 , ,	,1	
$(A)(B)_{10}$	٥	0	1	0		0	1	0		0	I	1	
11	٥	0	0	1	- 1	0	0	1	1	0	0	2 ,	10 kHz
12	٥	0	0	0	0	1	1	1	1	0	0	4	
13	0	0	0	0	0	0	0	0	0	1		8	
20	0	0	1	0		0		0	1	0	1 ;	1, 1,	
21	٥	0	0	I		0	0	-	1	0	0	2	100 kHz
22	0	0	0 .	0	0	0	0	0	0	1	1	8	V. DO KINA
23	0	0	0	0	0	1	I	ı	1	0	0	4	1/2 1/4 1/4 1/4 1/4 1/4 1/4 1/4 1/4 1/4 1/4

	J-4					
$\subset$	-0		144MHz	145MHz	146MHz	147MHz
48	0	4 simplex	ı	1	0	. 0
4S 4S	0	4 simplex	ı	1	0	0
6S	0	6 simplex	0	0	ı	1
6S	0	6 simplex	0	0	I	1
4M	0	6 minus "TX"	l	ı	0	0
6M	0	6 minus "TX"	0	0	. 1	1
6P	0	6 plus "TX"	0	0	1	1 .
Т6	0					,
R6	0					

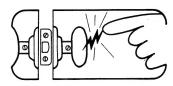
X50-1560-10 info to switch on Q1-Q5 and Q6 Local OSC

#### <TERMINALS>

33

	/ I E !!!!	INALO /				
	51 01 30 31	5 kHz Signal	R6 UI OA RO	+6 VDC in RX Unlock indicate On Air Rotary Switch Active Common B+	T9 TB SB SBS ST	Transmit +9 VDC +9 VDC when tone switch o
	32 }	Megahertz sig	CB MC NR MR	Memory cancel Normal Memory Read	DS LR LT	Diode switch for antenna Receive HET OSC Transmit HET OSC
	11 12 13	100 kHz	MW M6 13.8	Memory Write +6 VDC memory on Raw B+	PRO RFO FIB DRB	Protection signal RF out Final B+ Drive B+
£	20 21 22 23	10 kHz	CM AF SC	Center meter Audio Freq. Squelch Control +6 VDC when SQ active	RFI L BA FB	RF in Low Power Base Q102 Emitter of Q102
	4S	144 simplex	SQ	Squelch VR		
¥	6S	146 simplex	SM	S meter signal		
	4m 6m	144 offset ⊖ 146 offset ⊖	E S VCT	Earth Speaker Vari cap tune		
	6P T6	146 offset ⊕ +6 VDC in TX	MIC TON	MIC Tone signal in		en de la companya de La companya de la co

#### STATIC AWARENESS



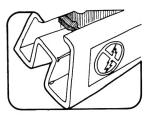
Some semiconductors and custom IC's can be damaged by electrostatic discharge during handling. This notice explains how you can minimize the chances of destroying such devices by:

- 1. Knowing that there is a problem.
- 2. Learning the guidelines for handling them.
- 3. Using the procedures, and packaging and bench techniques that are recommended.

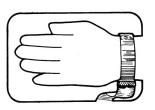
The following practice should be followed to minimize damage to S.S. devices.



1. MINIMIZE HANDLING



2. KEEP PARTS IN ORIGINAL CONTAINERS UNTIL READY FOR USE.



3. DISCHARGE PERSONAL STATIC BEFORE HANDLING DEVICE



4. HANDLE S.S. DEVICES BY THE BODY

WARNING: INDICATES USAGE OF MOS DEVICE(S)
WHICH MAY BE DAMAGED BY STATIC
DISCHARGE USE SPECIAL HANDLING.

CAUTION: SUBJECT TO DAMAGE BY STATIC

ELECTRICITY.

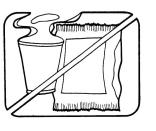
(From: Fluke model 12,19A freq, counter manual.)



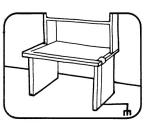
5. USE ANTI-STATIC CONTAINERS FOR HANDLING AND TRANSPORT



6. DO NOT SLIDE S.S. DEVICES OVER ANY SURFACE.



7. AVOID PLASTIC, VINYL AND STYRAFORM IN WORK AREA.



- 8. HANDLE S.S. DEVICES ONLY AT A STATIC-FREE WORK STATION.
- 9. ONLY GROUNDED TIP SOLDER-SUCKERS SHOULD BE USED.
- 10. ONLY GROUNDED TIP SOLDERING IRON SHOULD BE USED.

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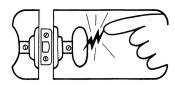
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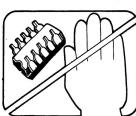
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DEVICE

h on



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# SPECIFICATIONS [K, W type]

**GENERAL** 

Mode:

Transistors: 48 (K), 47 (W) Semiconductors:

> FETs: ICs:

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Diodes: 88 (K), 77 (W)

144.00 to 147.995 MHz (K), 144.00 to 145.995 MHz (W) Frequency Range:

Digital control of phase locked VCO Frequency Synthesizer:

Better than ±750 Hz at 25°C Synthesizer Stability:

800 (K), 400 (W) No. of Channels:  $-20 \text{ to } +50^{\circ}\text{C}$ **Operating Temperature:** 

11.5V DC to 16.0V DC (13.8V DC standard) Power Voltage:

Negative grounding Grounding:

 $50\Omega$ Antenna Impedance:

Less than 0.5A in receive with no input signal DC Current:

Less than 6A in HI transmit

(at 13.8V DC)

161 mm (6-5/16") wide Dimensions:

> 61 mm (2-3/8") high 230 mm (9-1/16") deep

1.75 kg (3.85 lbs) Approx. Weight:

TRANSMITTER SECTION

High: 25 watts (min.) **RF Output Power:** 

Low: 5 watts approx. (adjustable to 25 watts)

Modulation: Variable reactance direct shift

+5 kHz Max. Frequency Deviation:

Less than -60 dB**Spurious Radiation:** 

 $600\Omega$ **Touch Tone Input Impedance:** 

Dynamic microphone with PTT switch,  $500\Omega$ Microphone:

**RECEIVER SECTION** 

Double superheterodyne Circuitry:

IF 10.7 MHz Intermediate Frequency:

> IF 455 kHz 2nd

Less than 0.4  $\mu$ V for 20 dB quieting Sensitivity:

(Less than 1  $\mu$ V for 30 dB S/N)

Less than 0.25 μV **Squelch Sensitivity:** 

Better than 12 kHz at 6 dB down Pass Band Width:

Better than 76 dB at 30 kHz (K), 70 dB at 25 kHz (W) of adjacent channel Selectivity (2 Signal):

Better than 70 dB Image Rejection: Better than 60 dB Spurious Interference:

Better than 66 dB (K), 60 dB (W) Intermodulation:

More than 1.5 watts across  $8\Omega$  load (10% distortion) Audio Output:

NOTE: The circuit and ratings may change without notice due to developments in technology.

#### KENWOOD CORPORATION

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